



212761US99

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Robert LEMPKOWSKI, et al.

SERIAL NO: 09/928,356

GAU: 2815

FILED: August 14, 2001

EXAMINER: BAUMEISTER

FOR: STRUCTURE AND METHOD FOR FABRICATING SEMICONDUCTOR STRUCTURES AND DEVICES FOR DETECTING AN OBJECT

2815
#7 135
3-26-03
ext 10

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references were submitted in application Serial No. 09/908,888 according to the attached copy of a Granted Petition. This application contains related subject matter.
- ☒ A check is attached in the amount required under 37 CFR §1.17(p).

RECEIVED
MAR 21 2003
TECHNOLOGY CENTER
2800

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

03/19/2003 CV0111 00000051 09928356

01 FC:1806

180.00 OP

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



22850

Richard L. Treanor

Registration No. 36,379

Tel. (703) 413-3000
Fax. (703) 413-2220
(OSMMN 03/02)



JUL 31 2001

~~JUL 30 2002~~RECEIVED: 8-5-02
OBLON SPIVAK MCLELLAND
MAIER & NEUSTADT, P.C.

DOCKETING DEPT.

Initials/Date Docketed: 11-8-02
Type of Resp(s): _____
Due Date(s): _____OBLON SPIVAK MCLELLAND MAIER & NEUSTADT PC
FOURTH FLOOR
1755 JEFFERSON DAVIS HIGHWAY
ARLINGTON VA 22202In re Application of
Vierira, et al.
Application No. 09/908,888
Filed: July 20, 2001
For: Fabrication Of A Wavelength
Locker Within A Semiconductor
Structure
Attorney Docket No. 211692US99: RESPONSE TO PETITION
: UNDER 37 CFR 1.182
: SEEKING SPECIAL
: TREATMENT OF DISCLOSURE
: STATEMENTS, AND
: DECISION ON PETITION
: UNDER 37 CFR 1.183
: SEEKING WAIVER OF
: REQUIREMENTS UNDER
: 37 CFR 1.98

This is a response to a petition under 37 CFR 1.182 filed on April 12, 2002 and supplements filed on July 1, 2002 and on July 12, 2002. The § 1.182 petition requests special treatment of disclosure statements filed pursuant to 37 CFR 1.98. Additionally, the petition requests waiver of the rules which waiver is treated as a request under 37 CFR 1.183, for relief from the current requirements for Information Disclosure Statements under 37 CFR 1.98. The request for special treatment and waiver are made in view of the need to file multiple applications relating to different aspects of a particular invention. The § 1.182 petition also contains a request seeking permission to submit prior art submissions on compact disc and the establishment and searching of an Official classification(s) based on the prior art submission. The petition under 37 CFR 1.183, is requesting relief from the § 1.98 provision which requires filing paper copies of references in each of many related applications where the references are being cited by Petitioner.

The petition under 37 CFR 1.182 requesting special treatment of disclosure statements, and the petition under 37 CFR 1.183 regarding the submission of a reduced number of paper copies of IDS references is GRANTED IN PART to the extent set forth below.

The Decision is set forth in five parts:

- Part I. Background
- Part II. Petition Under 37 CFR 1.182 - Special Treatment
- Part III. Petition Under 37 CFR 1.183 - Paper Copies
- Part IV. Summary
- Part V. Further Correspondence

Part I. Background

The instant application filed under 35 U.S.C. 111 is one of about 330 U.S. applications (either filed or to be filed) relating to

RECEIVED
MAR 21 2003
TECHNOLOGY CENTER

different aspects of an invention listed in the July 1, 2002 supplement to the petition. An appendix prepared by Technology Center 2800 indicates approximately 300 of the applications have been classified for examination in Technology Center 2800. The balance of about 30 applications are in five other Technology Centers. The July 12, 2002 supplement to the petition indicates that an Information Disclosure Citation List has in excess of 400 reference citations.

Petitioner's submission of an Information Disclosure Statement is taken as an attempt to comply with 37 CFR 1.56(b)(1) that requires disclosure to the Office of information that "establishes, by itself or in combination with other information, a prima facie case of unpatentability of a claim...." Such disclosure can be made by an Information Disclosure Statement (IDS) in the manner prescribed by 37 CFR 1.97 and 1.98.

Part II. Petition Under 37 CFR 1.182 - Special Treatment

The petition requests the establishment of an Official search classification containing all of the references cited in the IDS and that the examiners be required to search that classification.

As is the case with all search Digests, their creation and usefulness is continually evaluated. The Office will create and place appropriate references in Digests as they are discovered. The Office will not commit to placement of each IDS citation, made in all of the bulk filing applications, in any Digest(s) as the particular relevancy of the citations at this time is uncertain because petitioner has supplied no explanation of any of the citations. The Office will not require that any digest(s) created be searched for each of the bulk filing applications as the appropriate search for any particular application is within the determination and discretion of individual examiner based on the claim(s) of that application.

The petition also mentions the submission of additional copies of the references on compact disc for the examiner's convenience which appear to be courtesy copies. Courtesy copies will not be made part of the Official record of any application and cannot be relied upon for meeting any requirement for the submission of an information disclosure statement. There is insufficient information in the petition concerning the data formats and software requirements to accord the compact discs any other status. Further, as discussed below, the Office has a procedure for electronically submitting citations without paper copies for an Information Disclosure Statement. Hence it is not clear why relief is required under § 1.182. In view of the relief granted below, and that no specific action is requested concerning the compact disc submission, no further discussion of the compact discs is required in this decision.

Petition under § 1.182 is Dismissed.

Part III. Petition Under 37 CFR 1.183 - Paper Copies

37 CFR 1.98 requires that any information disclosure statement provide a copy of all patents, publications or other information submitted under 37 CFR 1.97 for consideration by the Office. 37 CFR 1.97 notes that information disclosure statements are considered in regard to the application in which they are filed. See also MPEP 609, pages 600-118 and 600-119.

Paper copies: Petitioner notes that the instant application is one of about 330 bulk filing applications that will be or have been filed in regard to a particular technology. Accordingly, Petitioner requests that individual paper copies of each citation brought to the attention of the Office in regard to the instant individual application, the "holding" application, not be required to be submitted in each related "bulk filing" application. Rather, it is requested that three complete sets of paper copies be permitted to be filed as a substitute for filing in each application.

Rather than be required to submit, via a paper copy, 400 reference in each of 330 applications, Petitioner seeks to have:

(1) Three complete sets of paper copies of each IDS citation submitted;

(2) One application (the instant application) identified as a "holding" application which would contain one complete set of paper copies of references; the paper copies of U.S. patents to be submitted in only the "holding" application;

(3) The other related pending U.S. applications, hereafter referred to as the "bulk filing" applications, be exempt from containing a paper set of the references; the bulk filing applications will contain other information, e.g., a copy of the decision on petition permitting such procedure, a copy of the Form 1449 (or equivalent). The petition does not indicate whether the paper references that are to be submitted as a numbered compendium, which numbering will correspond to the numbering in a PTO-1449 form.

(4) The information supplied via the bulk filing IDS will be updated approximately monthly.

Once past the initial IDS submission, the petition proposes the waiver to apply to updates.

Suspension of action: In view of the use of the instant application as a holding application (to contain a complete set of paper copies of reference citations, which can be consulted by the examiner when examining any of the other bulk filing applications that have a Form 1449 but not the paper copies of the references), the petition does not address how upon allowance the instant holding application will be treated. Whether the application can remain as the holding application without a suspension of action is not addressed. An alternative not discussed in the petition is that an alternate application may be designated as the holding application.

Termination: Petitioner does not seek a specific right of termination. Termination by the Office is to be by written notice to the attorney giving a 2 month period. Termination by Petitioner is to be by returning to compliance with 37 CFR § 1.98. The Office will accept and specifically reserve the right to terminate the waiver grant in regard to § 1.98(a)(2) without provision of reasons. Should a termination of the waiver be desired by the Office, the Office will provide written notice to the correspondence address of record. In such event, a two month period will be given where paper copies would have to be supplied in all applications where new citations are made. Termination by Applicant may be by returning to compliance with § 1.98(a)(2) without formal notice thereof and no transition/continuing period after termination is required.

Different Technology Centers: It appears from the petition that Petitioner intends to cite every reference cited in any of the 330 applications in every other application. No references will be omitted because they are less relevant or cumulative of those already of record in a particular application. At least 30 of the applications are of such divergent technologies that they are in 5 technology centers outside Technology Center 2800. The applications outside Technology Center 2800 will be examined in areas without convenient access to the paper copies in Technology Center 2800. The 5 other technology centers have requested more access to the paper copies than the relief granting this petition for all 330 applications will afford. It is not clear from the petition why citing every reference in every application when they are in such diverse technologies is necessary or required by § 1.56. Relieving petitioner of the burden of filing paper copies in applications outside Technology Center 2800 will create an additional burden on the examiners of those applications. It is also possible for applicant to comply with 37 CFR 1.98 for U.S. Patents and Patent application publications by submitting references via "e-IDS."¹ Hence it appears that petitioner has not demonstrated why a waiver for those applications filed outside Technology Center 2800 is necessary.

Decision: 37 CFR 1.183 provides relief for extraordinary situations, when justice requires suspension of any requirement of the regulations which is not a requirement of the statutes. The instant petition urges that not only would applicant be spared the necessity of submitting duplicative paper copies of U.S. patents in over 300 applications, but also the Office would benefit from not having to handle and store the duplicative sets of copies. While there may be some negative effects from the Office's point of view in terms of making the copies available to different examiners handling the various applications, on balance, there is seen to be sufficient benefit to justify waiver in this instance for the applications filed in Technology Center 2800. With respect to those applications being examined outside

¹The instructions for submitting an e-IDS can be downloaded at:
http://www.uspto.gov/ebc/efs/downloads/documents/EFSePAVE_April23.pdf.

Technology Center 2800, on balance, the burden on petitioner is substantially less to provide an additional paper copy for each application with significantly less benefit to the Office waiving the requirement. Further with respect to other 30 applications the need to submit these references has not been established nor has petitioner addressed alternative methods of compliance.

Accordingly, the petition under 37 CFR 1.183 is granted to the extent indicated and under the terms and conditions as are set forth below.

The § 1.98(a)(2) requirement for (the submission of) a copy of each IDS citation in a bulk filing application will be waived in the bulk filing applications examined in Technology Center 2800 provided that the following 9 conditions are complied with:

- 1) Three paper copies of each IDS citation are or have been submitted to the Office;
- 2) Each (bulk filing) application for which waiver of § 1.98(a)(2) is desired refers to the instant holding application, such as by a claim of priority under 35 U.S.C. 120, or as containing related technology;
- 3) The information is or has also been cited in the holding application;

Note: Applicant is not required to cite in each bulk filing application every item of information that is cited in the instant holding application. Items should be cited in each bulk filing application on the basis of relevancy and materiality to the particular claims in the bulk filing application and what each piece of information teaches.

A waiver is not granted (for the requirement to supply a paper copy of an IDS citation in another bulk filing application) where the citation is not, or has not been, made in the instant holding application.

- 4) A copy of this Decision is filed in each bulk filing application for which waiver is requested;

- 5) Explanatory information related to a particular citation, such as the concise explanation of a foreign language reference under § 1.98(a)(2), once submitted in the holding application must be supplied in each bulk filing application where the citation is made.

- 6) The Office accepts and specifically reserves the right to terminate the waiver grant in regard to § 1.98(a)(2) without provision of reasons. In such event, a two month period will be given where paper copies would have to be supplied in all applications where new citations are made. Should a termination of the waiver be desired by the Office, the Office will provide written notice to the correspondence address of record. Termination by applicant may be by returning to compliance with § 1.98(a)(2) without formal notice thereof and no transition/continuing period after termination is required.

- 7) The grant of the § 1.183 petition re § 1.98(a)(2) does

not indicate that the Office would favorably treat a petition to suspend action under § 1.103(a) should the instant holding application be allowed. Issuance of the instant application as a patent is not seen to terminate its usefulness either: (1) as a holding application for references by examiners working on other related applications, or (2) as a vehicle for the storage of references to be cited even after the patent issues (35 U.S.C. 301, 37 CFR 1.501, and MPEP 2202). Should the instant application become abandoned, the issue of continued introduction of paper copies of new citations could be taken up at that time. The Office, however, may consider suspending or taking other appropriate action in the instant holding application in the event the holding application is allowed, if it is in the best interest of the Office to do so.

8) There will be no waiver of any aspects of 37 CFR 1.98 in any application after allowance or final rejection of that application.

9) The copies will be submitted as a compendium with the reference numbering in the Form 1449 corresponding to the presentation of the references in the compendium.

Part IV. Summary

The petition under 37 CFR 1.182 requesting special treatment by creation of special digests and accepting compact disc submissions is dismissed because there is no showing that the relief granted below under 37 CFR 1.183 is not sufficient for compliance with 37 CFR 1.56.

The petition under 37 CFR 1.183 agreeing to supply three copies of each IDS citation in a holding application and requesting waiver of the paper copy requirement for submission in every related application under § 1.98(a)(2) is granted for those applications examined in Technology Center 2800, however, the following is not agreed to:

- the waiver of supplying a paper copy of each reference in applications examined outside Technology Center 2800.
- the creation of Official search classifications and the mandatory search thereof.
- The establishment of an Official search classification containing all of the references cited in the IDS and that the examiners be required to search that classification.

Part V. Further Correspondence

Any correspondence with respect to this matter should be addressed as follows:

By mail: Assistant Commissioner for Patents
 Box DAC
 Washington, D.C. 20231

TC Assignment Appendix
Bulk Filing List With TC Assignment

Docket Number	Application #	Art Unit
	10125540	1631
	9984471	1641
	9624877	1725
	9911539	1725
	9911493	1743
	9832354	1753
	9842735	1765
	9884981	1765
	9911702	1765
	9921910	1765
	9975930	1765
	10124460	1765
	09273929	1765
	09662390	1765
	9905110	1772
	9621771	1775
	9870830	1775
	9871958	1775
	9901109	1775
	9960402	1775
	09274268	1775
	09465623	1775
	09813779	1775
	9865446	2631
	9930171	2633
	09617640	2633
	9910032	2663
	10152783	2673
	09607239	2681
	09607420	2682
	9900885	2811
	10125486	2811
	10128262	2811
	10141876	2811
	10145734	2811
	10150065	2811
	09607386	2811
205954US-8737-8737-99	09607434	2811
205680US-8737-8737-99	09712425	2811
205890US-8737-8737-99	09721566	2811
2061 ssus-8737-s737-ss	09766046	2811
208836US-8737-8737-99	09861636	2811
210044US-8737-8737-99	09884150	2811
210790US-8737-8737-99	09897965	2811
210260US-8737-8737-99	09900887	2811
211327US-8737-8737-99	09905869	2811
211318US-8737-8737-99	09905935	2811
211467US-8737-8737-99	09907705	2811
211685US-8737-8737-99	09908695	2811
211535US-8737-8737-99	09908860	2811
211689US-8737-8737-99	09908886	2811
211581US-8737-8737-99	09909936	2811
211891 US-8737-8737-99	09911455	2811
211804US-8737-8737-99	09911456	2811
211642US-8737-8737-99	09911465	2811
211805US-8737-8737-99	09911475	2811
213020US-8737-8737-99	09930247	2811

TC Assignment Appendix
Bulk Filing List With TC Assignment

Docket Number	Application #	Art Unit
214975US-8737-8737-99	09978096	2811
216416 US-8737-8737-99	09994066	2811
217300US-8737-8737-99	10017596	2811
217730US-8737-8737-99	10026446	2811
219105US-8737-8737-99	10062429	2811
220526 US-8737-236694-99	10091452	2811
	10137383	2812
	10150066	2812
205958US-8737-8737-99	09678372	2812
	09801881	2812
209888 US-8737-8737-99	09884082	2812
210236US-8737-8737-99	09900921	2812
210800US-8737-8737-99	09903741	2812
211147US-8737-8737-99	09903784	2812
211214US-8737-8737-99	09904892	2812
211398US-8737-8737-99	09905981	2812
211691 US-8737-8737-99	09908902	2812
211699US-8737-8737-99	09909941	2812
211574US-8737-8737-99	09910022	2812
211644US-8737-8737-99	09910754	2812
21217005-8737-8737-99	09921901	2812
21288605-8737-8737-99	09929021	2812
216420US-8737-8737-99	09993523	2812
218840US-8737-8737-99	10059411	2812
	10134506	2813
205962US-8737-8737-99	09624526	2813
205881 US-8737-8737-99-CIP	09780119	2813
291419US-8737-8737-99	09906783	2813
21189705-8737-8737-99	09911496	2813
211806US-8737-8737-99	09911496	2813
29 2171 US-8737-8737-99	09921905	2813
215930US-8737-8737-99	09986899	2813
	9930275	2814
	10137369	2814
	10140939	2814
205949US-8737-8737-99	09607408	2814
205924US-8737-8737-99	09621779	2814
205925US-8737-8737-99	09624699	2814
205917US-8737-8737-99	09642558	2814
205906US-8737-8737-99-CIP	09740219	2814
208835US-8737-8737-99	09861638	2814
208833US-8737-8737-99	09861639	2814
209079US-8737-8737-99	09865428	2814
209117US-8737-8737-99	09865429	2814
209080US-8737-8737-99	09865448	2814
208889US-8737-8737-99	09865449	2814
209995US-8737-8737-99	09882063	2814
210295US-8737-8737-99	09897059	2814
210789US-8737-8737-99	09897968	2814
211334US-8737-8737-99	09905980	2814
211323US-8737-8737-99	09906138	2814
211662US-8737-8737-99	09908888	2814
210139US-8737-8737-99	09909939	2814
211580US-8737-8737-99	09910019	2814
211719US-8737-8737-99	09911458	2814
211920US-8737-8737-99	09911459	2814
211720US-8737-8737-99	09911478	2814
21195505-8737-8737-99	09911488	2814

TC Assignment Appendix
Bulk Filing List With TC Assignment

Docket Number	Application #	Art Unit
21202205-8737-8737-99	09911518	2814
21241905-8737-8737-99	09921898	2814
21287705-8737-8737-99	09929018	2814
21294505-8737-8737-99	09929748	2814
212949US-8737-8737-99	09930188	2814
212960US-8737-8737-99	09930259	2814
212958US-8737-8737-99	09930278	2814
215560US-8737-8737-99	09983859	2814
21 B359US 8737-8737-99	10053588	2814
205920US-8737-8737-99-C1P	09607207	2815
20591 OUS-8737-8737-99	09621130	2815
205927US-8737-8737-99	09624691	2815
205918US-8737-8737-99	09629283	2815
205877US-8737-8737-99	09692568	2815
205887US-8737-8737-99	09733181	2815
205922US-8737-8737-99-C1P	09755340	2815
205961 US-8737-8737-99	09755341	2815
205960uS-8737-8737-99	09755691	2815
205966us-8737-8737-99-cIP	09824376	2815
205967US-8737-8737-99-CIP	09824615	2815
209279US-8737-8737-99	09849172	2815
209340US-8737-8737-99	09870592	2815
209997US-8737-8737-99	09882062	2815
210140US-8737-8737-99	09884982	2815
210243US-8737-8737-99	09900882	2815
210798US-8737-8737-99	09901601	2815
210827US-8737-8737-99	09903742	2815
211400US-8737-8737-99	09904841	2815
210828US-8737-8737-99	09905932	2815
211677US-8737-8737-99	09908892	2815
211675US-8737-8737-99	09910021	2815
211645US 8737-8737-99	09911412	2815
211894US-8737-8737-99	09911490	2815
212423US-8737-8737-99	09911491	2815
211896US-8737-8737-99	09911542	2815
2114.71 US-8737-8737-99	09911691	2815
21202405-8737-8737-99	09918801	2815
212543US-8737-8737-99	09924481	2815
21266905-8737-8737-99	09927396	2815
212761 US-8737-8737-99	09928356	2815
212954US-8737-8737-99	09929020	2815
29 287805-8737-8737-99	09929022	2815
212947US-8737-8737-99	09929261	2815
212944 US-8737-8737-99	09930145	2815
29290605-8737-8737-99	09930175	2815
212948US-8737-8737-99	09930176	2815
213012US-8737-8737-99	09930260	2815
212953US-8737-8737-99	09930261	2815
212959 US-8737-8737-99	09930276	2815
213130US-8737-8737-99	09934836	2815
215512US-8737-8737-99-CIP	09983854	2815
215878US-8737-8737-99-DIV	09986034	2815
219625US-8737-8737-99-DIV	10076450	2815
211573US-8737-8737-99	09909938	2816
211637US-8737-8737-99	09910799	2817
	10161743	2818
205955US-8737-8737-99	09609071	2818
205913U8-8737-8737-99	09656337	2818
205957US-8737-8737-99	09712875	2818

TC Assignment Appendix
Bulk Filing List With TC Assignment

Docket Number	Application #	Art Unit
205908US\$737-8737-99	09740268	2818
206160US-8737-8737-99	09753808	2818
205909US-.8737-8737-99	09822499	2818
205969US,8737-8737-99	09822499	2818
205971 US-8737-8737-99	09824259	2818
205970US-8737-8737-99	09824388	2818
209278US-8737-8737-99	09849159	2818
209280US-8737-8737-99-CIP	09859700	2818
209341 US-8737-8737-99	09870589	2818
209164US-8737-8737-99	09870828	2818
209166US-8737-8737-99	09870829	2818
210132US-8737-8737-99	09884149	2818
210148US-8737-8737-99	09885409	2818
211314US-8737-8737-99	09905868	2818
211422US-8737-8737-99	09906769	2818
211472US-8737-8737-99	09908898	2818
211670U&8737-8737-99	09910018	2818
211686US-8737-8737-99	09910020	2818
211640US-8737-8737-99	09910798	2818
21195805-8737-8737-99	09911429	2818
211584US-8737-8737-99	09911448	2818
211578US-8737-8737-99	09911628	2818
211425US-8737-8737-99	09911629	2818
215562 US-8737-8737-99	09983869	2818
217459US-8737-8737-99	10020900	2818
218843US 8737-8737-99	10059409	2818
215820US 8737-8737-99	09986534	2821
208826US-8737-8737-99	09861637	2822
209078US-8737-8737-99	09865447	2822
209077US-8737-8737-99	09866637	2822
210792US-8737-8737-99	09899997	2822
211469 US-8737-8737-99	09907707	2822
211534US-8737-8737-99	09908707	2822
211684US-8737-8737-99	09908887	2822
211673US-8737-8737-99	09908897	2822
211674US-8737-8737-99	09909937	2822
211956 US-8737-8737-99	09911447	2822
211850US.8737-8737-99	09911507	2822
212021 US-8737-8737-99	09911517	2822
21202505-87378737-99	09911627	2822
212131 US-8737-8737-99	09919967	2822
21290705-8737-8737-99	09930170	2822
	10136324	2823
205959US-87378737-99	09689583	2823
210150US-8737-8737-99	09884983	2823
210244US-8737-8737-99	09900883	2823
210216US-8737-8737-99	09903743	2823
211413US-8737-8737-99	09905863	2823
211315US-8737-8737-99	09905933	2823
211474US-8737-8737-99	09907703	2823
211555US-8737-8737-99	09908883	2823
211671 US-8737-8737-99	09910023	2823
211676US-8737-8737-99	09910034	2823
211618US-8737-8737-99	09910753	2823
29 2955US-8737-8737-99	09930444	2823
215873US-8737-8737-99-D IV	09986024	2823
216598US-8737-8737-99-DN	09993514	2823
205889US-8737737-99	09733688	2824
205914US-8737-8737-99	09795784	2824

TC Assignment Appendix
Bulk Filing List With TC Assignment

Docket Number	Application #	Art Unit
210259US-8737-873799	09897128	2824
210784US-8737-8737-99	09905098	2824
211577US-8737-9737-99	09909905	2824
21301 OUS-8737-8737-99	09930308	2824
	10125410	2825
205912US-8737\$737 99	09624690	2825
205893US-8737-873799	09625100	2825
210788US-8737-8737-99	09901110	2825
211317US-8737-8737-99	09906730	2825
211688US-8737-8737-99	09908891	2825
211579US-8737-8737-99	09909940	2825
211917US-8737-8737-99	09911460	2825
205973US-8737-8737-99	09584601	2826
205938US-8737-8737-99	09624296	2826
205934US-8737-8737.89	09624754	2826
205884US-8737-8737-99-CIP	09758723	2826
205968US-8737-8737-99	09824273	2826
206669US-8737-873799	09838273	2826
209491 US-8737-8737-99-CIP	09840213	2826
209284U S,8737-8737-99	09842734	2826
209281 US-8737-8737-99	09853744	2826
209336US-8737-8737-99	09870834	2826
209505US-8737-8737-99	09874984	2826
210826US-8737-873799	09904894	2826
210786US-8737-87379	09905902	2826
211326US-8737-8737-99	09905903	2826
211328US-8737-8737-99	09905930	2826
211325US-8737-8737-99	09905934	2826
211431 US-8737-8737-99	09906784	2826
211468US-8737-8737-99	09907704	2826
211672 US-8737-8737-99	09910024	2826
211582US-8737-8737-99	09910044	2826
21202005-8737-8737-99	09911444	2826
211724us-6737-8737-99	09911464	2826
211803US-8737-8737-99	09911473	2826
211690US-8737-8737-99	09911484	2826
211890US-8737-8737-99	09911494	2826
211722US-8737-8737-99	09911543	2826
212421 U&8737-8737-99	09921894	2826
292946US-8737-8737-99	09929024	2826
213009US-8737-8737-99	09930254	2826
21290905-8737-8737-99	09930270	2826
	9985757	2828
209282U5-8737-873799	09852109	2828
210787US-8737-8737-99	09901905	2828
210785US-8737-8737-99	09903740	2828
210257US-8737-8737-99	09910035	2828
21217305-8737-8737-99	09921900	2828
213011 US-8737-8737-99	09930243	2828
	10166196	2829
206166US-8737-8737-99	09425945	2829
209696US-8737-8737-99	09882064	2829
211324US-8737-8737-99	09904895	2829
211332 US-87378737-99	09905116	2829
211893US-8737-8737-99	09911445	2829
211723US-8737-8737-99	09911446	2829
21181 OUS-8737-8737-99	09911495	2829
215295US-8737-8737-99	09983326	2829

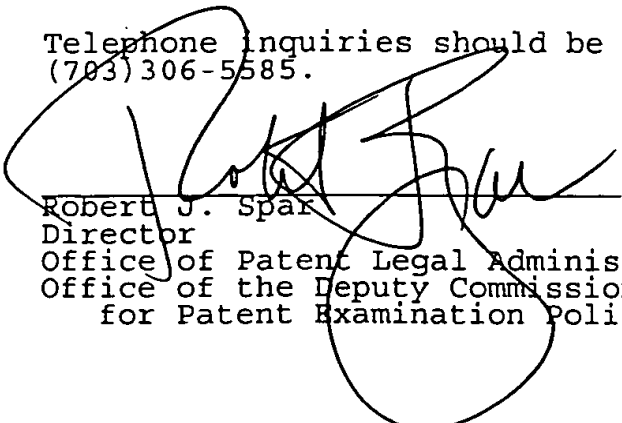
TC Assignment Appendix
Bulk Filing List With TC Assignment

Docket Number	Application #	Art Unit
205915US-8737-9737-99	09624803	2834
211916US-8737-8737-99	09911487	2839
217731 US-8737-8737-99	10026812	2841
	10151950	2851
217354US-8737-8737-99	10020898	2861
205972US-8737-873799	09624698	2872
205939US-8737 837-99	09669602	2873
205950U737-8737-99	09607236	2874
205951 US-8737-8737-99	09607744	2874
205947US-8737-8737-99	09608807	2874
209409US-8737-8737-99	09870836	2874
209162US-87378737-99	09870837	2874
217678US-8737-8737-99	09908885	2874
210824US-8737-8737-99	09909906	2874
211854US-8737-8737-99 -	09911457	2874
211808US-8737-8737-99	09911466	2874
211807US-8737-8737-89	09911469	2874
211911 US-8737-8737-99	09911472	2874
21195705-8737-8737-99	09911492	2874
21209905-8737-8737-99	09918802	2874
21209805-8737-8737-99	09919927	2874
212950US-8737-8737-99	09929019	2874
215539US-8737-8737-99-CONT	09983866	2874
205949 US-8737-8737-99	09607237	2876
205944US-8737-8737 99	09609262	2877
209403US-8737-8737-99	09870831	2877
209338US-8737-8737-99	09870832	2877
209695US-8737-8737-99	09882067	2878
209402US-8737-8737-99	09870835	2881
210794US-8737-8737-99	09899996	2881
211427US-8737-8737-99	09906782	2881
21242505-8737-8737-99	09921895	2881
212426US-8737-8737-99	09921896	2881
212590US-8737-8737-99	09927393	2881
209342US-87378737-99	09870833	2882
	9905115	3662
	9911420	3663
	09607722	3736

By FAX: (703) 872-9005

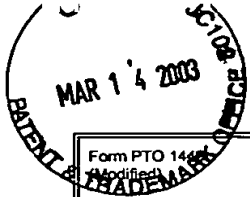
By hand: Crystal Plaza Four, Suite 3C23
2201 South Clark Place
Arlington, VA 22202

Telephone inquiries should be directed to Michael L. Lewis at
(703) 306-5585.



Robert J. Spar
Director
Office of Patent Legal Administration
Office of the Deputy Commissioner
for Patent Examination Policy

Attachment: TC Assignment Appendix

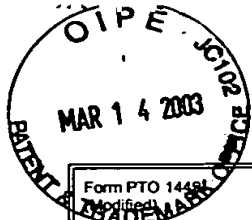


Form PTO 1449 Modified TRADEMARK U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 212761US99	SERIAL NO. 09/928,356
	APPLICANT Robert LEMPKOWSKI, et al.	
	FILING DATE August 14, 2001	GROUP 2815

LIST OF REFERENCES CITED BY APPLICANT

U.S. PATENT DOCUMENTS

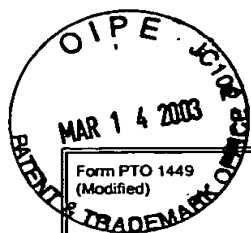
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BWB	AA	3,802,967	04/09/74	Ladany et al.			
	AB	4,174,422	11/13/79	Matthews et al.			
	AC	4,404,265	09/13/83	Manasevit			
	AD	4,482,906	11/13/84	Hovel et al.			
	AE	4,523,211	06/11/85	Morimoto et al.			
	AF	4,661,176	04/28/87	Manasevit			
	AG	4,793,872	12/27/88	Meunier et al.			
	AH	4,846,926	07/11/89	Kay et al.			
	AJ	4,855,249	08/08/89	Akasaki et al.			
	AI	4,891,091	01/02/90	Shastri			
	AK	4,912,087	03/27/90	Aslam et al.			
	AL	4,928,154	05/22/90	Umeno et al.			
	AM	4,963,949	10/16/90	Wanlass et al.			
	AN	5,141,894	08/25/92	Bisaro et al.			
	AO	5,159,413	10/27/92	Calviello et al.			
	AP	5,173,474	12/22/92	Connell et al.			
	AQ	5,221,367	06/22/93	Chisholm et al.			
	AR	5,225,031	07/06/93	McKee et al.			
	AS	5,358,925	10/25/94	Neville Connell et al.			
	AT	5,393,352	02/28/95	Summerfelt			
	AU	5,418,216	05/23/95	Fork			
	AV	5,450,812	09/19/95	McKee et al.			
	AW	5,478,653	12/26/95	Guenzer			
	AX	5,482,003	01/09/96	McKee et al.			
	AY	5,514,484	05/07/96	Nashimoto			
	AZ	5,556,463	09/17/96	Guenzer			
	BA	5,588,995	12/31/96	Sheldon			
	BB	5,670,798	09/23/97	Schetzina			
	BC	5,733,641	03/31/98	Fork et al.			
	BD	5,735,949	04/07/98	Manti et al.			
	BE	5,741,724	04/21/98	Ramdani et al.			
	BF	5,810,923	09/22/98	Yano et al.			
	BG	5,830,270	11/03/98	McKee et al.			
	BH	5,912,068	06/15/99	Jia			
	BI	6,020,222	02/01/00	Wollesen			
	BJ	6,045,626	04/04/00	Yano et al.			
	BK	6,064,078	05/16/00	Northrup et al.			
	BL	6,064,092	05/16/00	Park			
	BM	6,096,584	08/01/00	Ellis-Monaghan et al.			
	BN	6,103,008	08/15/00	McKee et al.			
	BO	6,136,666	10/24/00	So			
	BP	6,174,755	01/16/01	Manning			
	BQ	6,180,486	01/30/01	Leobandung et al.			



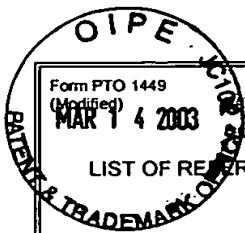
Form PTO 1449 Modified	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 212761US99	SERIAL NO. 09/928,356
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Robert LEMPKOWSKI, et al.	
		FILING DATE August 14, 2001	GROUP 2815

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BWB	CA	3,766,370	10/16/73	Walther			
	CB	4,006,989	02/08/77	Andringa			
	CC	4,284,329	08/18/81	Smith et al.			
	CD	4,777,613	10/11/98	Shahan et al.			
	CE	4,802,182	01/31/89	Thornton et al.			
	CF	4,882,300	11/21/89	Inoue et al.			
	CG	4,896,194	01/23/90	Suzuki			
	CH	4,999,842	03/12/91	Huang et al.			
	CI	5,081,062	01/14/92	Vasudev et al.			
	CJ	5,155,658	10/13/92	Inam et al.			
	CK	5,248,564	09/28/93	Ramesh			
	CL	5,260,394	11/09/93	Tazaki et al.			
	CM	5,270,298	12/14/93	Ramesh			
	CN	5,286,985	02/15/94	Taddiken			
	CO	5,310,707	05/10/94	Oishi et al.			
	CP	5,326,721	07/05/94	Summerfelt			
	CQ	5,404,581	04/04/95	Honjo			
	CR	5,418,389	05/23/95	Watanabe			
	CS	5,436,759	07/25/95	Dijaii et al.			
	CT	5,576,879	11/19/96	Nashimoto			
	CU	5,606,184	02/25/97	Abrokwah, et al.			
	CV	5,640,267	06/17/97	May et al.			
	CW	5,674,366	10/07/97	Hayashi et al.			
	CX	5,729,641	03/17/98	Chandonnet et al.			
	CY	5,790,583	08/04/98	Ho			
	CZ	5,825,799	10/20/98	Ho et al.			
	DA	5,857,049	01/05/99	Beranek et al.			
	DB	5,874,860	02/23/99	Brunel et al.			
	DC	5,926,496	07/20/99	Ho et al.			
	DD	5,937,285	08/10/99	Abrokwah, et al.			
	DE	5,981,400	11/09/99	Lo			
	DF	5,990,495	11/23/99	Ohba			
	DG	6,002,375	12/14/99	Corman et al.			
	DH	6,008,762	12/28/99	Nghiem			
	DI	6,055,179	04/25/00	Koganei et al.			
	DJ	6,107,653	08/22/00	Fitzgerald			
	DK	6,113,690	09/05/00	Yu et al.			
	DL	6,114,996	09/05/00	Nghiem			
	DM	6,121,642	09/19/00	Newns			
	DN	6,128,178	10/03/00	Newns			
	DO	6,143,072	11/07/00	McKee et al.			
	DP	6,184,144	02/06/01	Lo			
	DQ	6,222,654	04/24/01	Frigo			



Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 212761US99		SERIAL NO. 09/928,356	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Robert LEMPKOWSKI, et al.		GROUP	
				FILING DATE August 14, 2001		2815	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BHW	EA	4,484,332	11/20/84	Hawrylo			
	EB	4,815,084	03/21/89	Scifres et al.			
	EC	4,876,219	10/24/89	Eshita et al.			
	ED	4,963,508	10/16/90	Umeno et al.			
	EE	5,060,031	10/22/91	Abrokwah, et al.			
	EF	5,063,166	11/05/91	Mooney et al.			
	EG	5,116,461	05/26/92	Lebby et al.			
	EH	5,127,067	06/30/92	Delcoco et al.			
	EI	5,144,409	09/01/92	Ma			
	EJ	5,293,050	03/08/94	Chapple-Sokol et al			
	EK	5,356,831	10/18/94	Calviello et al.			
	EL	5,391,515	02/21/95	Kao et al.			
	EM	5,442,191	08/15/95	Ma			
	EN	5,444,016	08/22/95	Abrokwah, et al.			
	EO	5,480,829	01/02/96	Abrokwah, et al.			
	EP	5,528,414	06/18/96	Oakley			
	EQ	5,614,739	03/25/97	Abrokwah et al.			
	ER	5,729,394	03/17/98	Sevier et al.			
	ES	5,731,220	03/24/98	Tsu et al.			
	ET	5,764,676	06/09/98	Paoli et al.			
	EU	5,777,762	07/07/98	Yamamoto			
	EV	5,778,018	07/07/98	Yoshikawa et al.			
	EW	5,778,116	07/07/98	Tomich			
	EX	5,801,105	09/01/98	Yano et al.			
EY	5,828,080	10/27/98	Yano et al.				
EZ	5,858,814	01/12/99	Goossen et al.				
FA	5,861,966	01/19/99	Ortel				
FB	5,883,996	03/16/99	Knapp et al.				
FC	5,995,359	11/30/99	Klee et al.				
FD	6,058,131	05/02/00	Pan				
FE	6,137,603	10/24/00	Henmi				
FF	6,146,906	11/14/00	Inoue et al.				
FG	6,173,474	01/16/01	Conrad				
FH	6,180,252	01/30/01	Farrell et al.				
FI	4,242,595	12/30/0	Lehovec				
FJ	4,398,342	08/16/83	Pitt et al.				
FK	4,424,589	01/03/84	Thomas et al.				
FL	4,876,208	10/24/89	Gustafson et al.				
FM	4,482,422	11/84	McGinn et al.				
FN	4,667,088	05/19/87	Kramer				
FO	4,772,929	09/20/88	Manchester et al.				
FP	4,841,775	06/27/89	Ikeda et al.				
FQ	4,845,044	07/04/89	Ariyoshi et al.				



Form PTO 1449

(Modified)

MAR 14 2003

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

LIST OF REFERENCES CITED BY APPLICANT

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

APPLICANT

Robert LEMPKOWSKI, et al.

FILING DATE

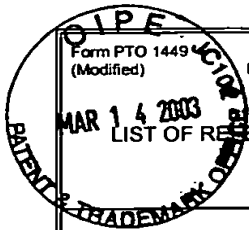
August 14, 2001

GROUP

2815

U.S. PATENT DOCUMENTS

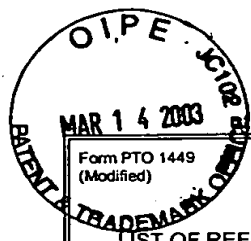
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BW B	GA	4,868,376	09/19/89	Lessin et al.			
	GB	4,885,376	12/05/89	Verkade			
	GC	4,888,202	12/89	Murakami et al.			
	GD	4,891,091	12/90	Wanlass et al.			
	GE	5,051,790	09/24/91	Hammer			
	GF	5,055,445	10/08/91	Belt et al.			
	GG	5,081,519	11/14/92	Nishimura et al.			
	GH	5,143,854	09/01/92	Pirung et al.			
	GI	5,185,589	02/09/93	Krishnaswamy et al.			
	GJ	5,191,625	03/02/93	Gustavsson			
	GK	5,194,397	03/16/93	Cook et al.			
	GL	5,208,182	05/04/93	Narayan et al.			
	GM	5,216,729	06/01/93	Berger et al.			
	GN	5,314,547	05/24/94	Heremans et al.			
	GO	5,352,926	10/04/94	Andrews			
	GP	5,356,509	10/18/94	Terranova et al.			
	GQ	5,371,734	12/06/94	Fischer			
	GR	5,372,992	12/94	Itozaki et al.			
	GS	5,405,802	04/11/95	Yamagata et al.			
	GT	5,442,561	08/15/95	Yoshizawa et al.			
	GU	5,453,727	09/26/95	Shibasaki et al.			
	GV	5,466,631	11/14/95	Ichikawa et al.			
	GW	5,473,047	12/05/95	Shi			
	GX	5,473,171	12/95	Summerfelt			
	GY	5,479,033	12/26/95	Baca et al.			
	GZ	5,486,406	01/23/96	Shi			
	HA	5,491,461	02/13/96	Partin et al.			
	HB	5,492,859	02/20/96	Sakaguchi et al.			
	HC	5,494,711	02/27/96	Takeda et al.			
	HD	5,504,035	04/02/96	Rostoker et al.			
	HE	5,504,183	04/02/96	Shi			
	HF	5,511,238	04/23/96	Bayraktaroglu			
	HG	5,512,773	04/96	Wolf et al.			
	HH	5,515,047	05/07/96	Yamakido et al.			
	HI	5,515,810	05/14/96	Yamashita et al.			
	HJ	5,519,235	05/96	Ramesh			
	HK	5,549,977	08/96	Jin et al.			
	HL	5,551,238	09/03/96	Prueitt			
	HM	5,552,547	09/03/96	Shi			
	HN	5,589,284	12/31/96	Summerfelt et al.			
	HO	5,602,418	02/11/97	Imai et al.			
	HP	5,633,724	05/27/97	King et al.			



U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 212761US99	SERIAL NO. 09/928,356
APPLICANT Robert LEMPKOWSKI, et al.		
FILING DATE August 14, 2001		GROUP 2815

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
gms	IA	5,650,646	07/22/97	Summerfelt			
	IB	5,656,382	08/12/97	Nashimoto			
	IC	5,659,180	08/19/97	Shen et al.			
	ID	5,661,112	08/26/97	Hatta et al.			
	IE	5,679,965	11/95	Schetzina			
	IF	5,725,641	03/10/98	MacLeod			
	IG	5,745,631	04/28/98	Reinker			
	IH	5,776,621	07/07/98	Nashimoto			
	II	5,777,350	07/07/98	Nakamura et al.			
	IJ	5,789,845	08/04/98	Wadaka et al.			
	IK	5,792,569	08/11/98	Sun et al.			
	IL	5,792,679	08/11/98	Nakato			
	IM	5,796,648	08/18/98	Kawakubo et al.			
	IN	5,801,072	09/01/98	Barber			
	IO	5,812,272	09/22/98	King et al.			
	IP	5,814,583	09/98	Itozaki et al.			
	IQ	5,825,055	10/20/98	Summerfelt			
	IR	5,827,755	10/27/98	Yonchara et al.			
	IS	5,833,603	11/10/98	Kovacs et al.			
	IT	5,838,035	11/17/98	Ramesh			
	IU	5,844,260	12/01/98	Ohori			
	IV	5,846,846	12/08/98	Suh et al.			
	IW	5,863,326	01/26/99	Nause et al.			
	IX	5,872,493	02/16/99	Ella			
	IY	5,879,956	03/99	Seon et al.			
	IZ	5,880,452	03/09/99	Plesko			
	JA	5,883,564	03/16/99	Partin			
	JB	5,907,792	05/25/99	Droopad et al.			
	JC	5,937,274	08/10/99	Kondow et al.			
	JD	5,948,161	09/07/99	Kizuki			
	JE	5,959,879	09/28/99	Koo			
	JF	5,966,323	10/99	Chen et al.			
	JG	5,987,011	11/16/99	Toh			
	JH	6,022,140	02/08/00	Fraden et al.			
	JI	6,022,410	02/08/00	Yu et al.			
	JJ	6,023,082	02/08/00	McKee et al.			
	JK	6,028,853	02/22/00	Haartsen			
	JL	6,049,702	04/11/00	Tham et al.			
	JM	6,078,717	06/20/00	Nashimoto et al			
	JN	6,088,216	07/00	Laibowitz et al.			
	JO	6,090,659	07/00	Laibowitz et al.			
	JP	6,107,721	08/22/00	Lakin			
	JQ	6,153,010	11/28/00	Kiyoku et al			

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

APPLICANT

Robert LEMPKOWSKI, et al.

LIST OF REFERENCES CITED BY APPLICANT

FILING DATE

August 14, 2001

GROUP

2815

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BWS	KA	6,153,454	11/28/00	Krivokapic			
	KB	6,191,011	02/01	Gilboa et al.			
	KC	6,204,737	03/20/01	Ella			
	KD	6,224,669	05/01/01	Yi et al.			
	KE	6,225,051	05/01/01	Sugiyama et al.			
	KF	6,241,821	06/05/01	Yu et al.			
	KG	6,265,749	07/24/01	Gardner et al.			
	KH	6,313,486	11/01	Kencke et al.			
	KI	6,316,832	11/13/01	Tsuzuki et al.			
	KJ	2002/0008234	01/02	Emrick			
	KK	3,670,213	06/13/72	Nakawaga et al.			
	KL	4,756,007	07/05/88	Qureshi et al.			
	KM	4,773,063	09/20/88	Hunsperger et al.			
	KN	5,394,489	02/28/95	Koch			
	KO	5,406,202	04/11/95	Mehrgardt et al.			
	KP	5,528,067	06/18/96	Farb et al.			
	KQ	5,572,052	11/05/96	Kashihara et al.			
	KR	5,767,543	06/16/98	Ooms et al.			
	KS	6,175,497	01/16/01	Tseng et al.			
	KT	6,197,503	03/06/01	Vo-Dinh et al.			
	KU	6,248,459	06/19/01	Wang et al.			
	KV	6,252,261	06/26/01	Usui et al.			
	KW	6,255,198	07/03/01	Linthicum et al.			
	KX	6,268,269	07/31/01	Lee et al.			
	KY	6,291,319	09/18/01	Yu et al.			
	KZ	6,316,785	11/13/01	Nunoue et al.			
	LA	6,343,171	01/29/02	Yoshimura et al.			
	LB	4,965,649	10/23/90	Zanio et al.			
	LC	6,253,649	05/01	Kawahara et al.			
	LD	6,211,096	04/01	Allman et al.			
	LE	6,239,449	05/29/01	Fafard et al.			
	LF	2001/0013313	08/16/01	Droopad et al.			
	LG	6,184,044	02/06/01	Sone et al.			
	LH	6,011,646	01/04/00	Mirkarimi et al.			
	LI	5,227,196	07/13/93	Itoh			
	LJ	6,150,239	11/21/00	Goesele et al.			
	LK	5,441,577	08/15/95	Sasaki et al.			
	LL	4,459,325	07/10/84	Nozawa et al.			
	LM	4,392,297	07/12/83	Little			
	LN	4,289,920	09/15/81	Hovel			
	LO	5,281,834	01/25/94	Cambou et al.			
	LP	4,901,133	02/13/90	Curran et al.			
	LQ	5,514,904	05/07/96	Onga et al.			

Form PTO 1449

(Modified)

MAR 14 2003

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Robert LEMPKOWSKI, et al.

FILING DATE

August 14, 2001

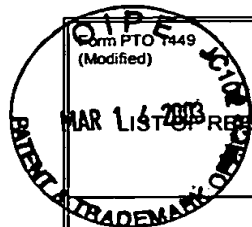
GROUP

2815

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BW	MA	5,553,089	09/03/96	Seki et al.			
	MB	5,528,057	06/18/96	Yanagase et al.			
	MC	6,229,159	05/08/01	Suzuki			
	MD	4,748,485	05/31/88	Vasudev			
	ME	4,984,043	01/08/91	Vinal			
	MF	5,754,319	05/19/98	Van De Voorde et al.			
	MG	6,108,125	08/22/00	Yano			
	MH	5,073,981	12/17/91	Giles et al.			
	MI	5,140,651	08/18/92	Soref et al.			
	MJ	5,610,744	03/11/97	Ho et al.			
	MK	6,362,017	03/26/02	Manabe et al.			
	ML	6,242,686	06/05/01	Kishimoto et al.			
	MM	5,689,123	11/18/97	Major et al.			
	MN	5,670,800	09/23/97	Nakao et al.			
	MO	5,067,809	11/26/91	Tsubota			
	MP	5,596,205	01/21/97	Reedy et al.			
	MQ	6,175,555	01/16/01	Hoole			
	MR	5,357,122	10/18/94	Okubora et al.			
	MS	4,084,130	04/11/78	Holton			
	MT	6,093,302	07/25/00	Montgomery			
	MU	6,372,813	04/16/02	Johnson et al.			
	MV	5,608,046	03/04/97	Cook et al.			
	MW	5,955,591	09/21/99	Imbach et al.			
	MX	6,022,963	02/08/00	McGall et al.			
	MY	6,083,697	07/04/00	Beecher et al.			
	MZ	5,063,081	11/05/91	Cozzette et al.			
	NA	5,479,317	12/26/95	Ramesh			
	NB	5,306,649	04/26/94	Hebert			
	NC	5,962,069	10/05/99	Schindler et al.			
	ND	5,541,422	07/30/96	Wolf et al.			
	NE	5,873,977	02/23/99	Desu et al.			
	NF	5,538,941	07/23/96	Findikoglu et al.			
	NG	6,046,464	04/04/00	Schetzina			
	NH	6,235,145	05/22/01	Li et al.			
	NI	5,610,744	03/11/97	Ho et al.			
	NJ	5,280,013	01/18/94	Newman et al.			
	NK	6,348,373 B1	02/19/02	Ma et al.			
	NL	6,339,664 B1	01/15/02	Farjady et al.			
	NM	4,439,014	03/27/84	Stacy et al.			
	NN	4,889,402	12/26/89	Reinhart			
	NO	5,963,291	10/05/99	Wu et al.			
	NP	6,011,641	01/04/00	Shin et al.			
	NQ	6,340,788 B1	01/22/02	King et al.			

RECEIVED
MAR 21 2003
TECHNOLOGY CENTER 2800



U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

APPLICANT

Robert LEMPKOWSKI, et al.

FILING DATE

August 14, 2001

GROUP

2815

REFERENCES CITED BY APPLICANT

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BWB	OA	5,807,440	09/15/98	Kubota et al.			
	OB	4,681,982	07/21/87	Yoshida			
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.			
	OD	4,452,720	06/05/84	Harada et al.			
	OE	3,935,031	01/27/76	Adler			
	OF	5,760,426	06/02/98	Marx et al.			
	OG	5,053,835	10/01/91	Horikawa et al.			
	OH	6,326,645 B1	12/04/01	Kadota			
	OI	5,770,887	06/23/98	Tadatomo et al.			
	OJ	6,372,356 B1	04/16/02	Thornton et al.			
	OK	4,774,205	09/27/88	Choi et al.			
	OL	6,359,330 B1	03/19/02	Goudard			
	OM	5,312,765	05/17/94	Kanber			
	ON	5,734,672	03/31/98	McMinn et al.			
	OO	6,367,699 B2	04/09/02	Ackley			
	OP	5,530,235	06/25/96	Stefik et al.			
	OQ	5,623,552	04/22/97	Lane			
	OR	5,481,102	01/02/96	Hazlerigg, Jr.			
	OS	6,134,114	10/17/00	Ungermann et al.			
	OT	5,984,190	11/16/99	Nevill			
	OU	5,789,733	08/04/98	Jachimowicz et al.			
	OV	5,753,300	05/19/98	Wessels et al.			
	OW	6,208,453	03/27/01	Wessels et al.			
	OX	5,886,867	03/23/99	Chivukula et al.			
	OY	5,028,976	07/02/91	Ozaki et al.			
	OZ	5,869,845	02/09/99	Vander Wagt et al.			
	PA	5,596,214	01/21/97	Endo			
	PB	6,391,674 B2	05/21/02	Ziegler			
	PC	6,275,122 B1	08/14/01	Speidell et al.			
	PD	6,238,946 B1	05/29/01	Ziegler			
	PE	6,210,988 B1	04/03/01	Howe et al.			
	PF	6,392,257	05/21/02	Ramdani et al.			
	PG	4,442,590	04/17/84	Stockton et al.			
	PH	5,603,764	02/18/97	Matsuda et al.			
	PI	6,087,681	06/11/00	Shakuda			
	PJ	5,132,648	07/21/92	Trinh et al.			
	PK	6,427,066	07/30/02	Grube			
	PL	2002/0072245	06/13/02	Ooms et al.			
	PM	6,278,138 B1	08/21/01	Suzuki			
	PN	5,888,296	03/30/99	Ooms et al.			
	PO	5,198,269	03/30/93	Swartz et al.			
	PP	2002/0030246	03/14/02	Eisenbeiser et al.			
	PQ	2002/0047143	04/25/02	Ramdani et al.			

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Robert LEMPKOWSKI, et al.

FILING DATE

August 14, 2001

GROUP

2815

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BWB	QA	5,776,359	07/07/98	Schultz et al.			
	QB	5,569,953	10/29/96	Kikkawa et al.			
	QC	5,834,362	11/10/98	Miyagaki et al.			
	QD	6,248,621 B1	06/19/01	Wilk et al.			
	QE	5,266,355	11/30/93	Wernberg et al.			
	QF	6,277,436 B1	08/21/01	Stauf et al.			
	QG	6,039,803	03/21/00	Fitzgerald et al.			
	QH	5,619,051	04/08/97	Endo			
	QI	5,420,102	05/30/95	Harshavardhan et al.			
	QJ	5,210,763	05/11/93	Lewis et al.			
	QK	5,103,494	04/07/92	Mozer			
	QL	4,594,000	06/10/86	Falk et al.			
	QM	4,297,656	10/27/81	Pan			
	QN	5,244,818	09/14/93	Jokers et al.			
	QO	6,048,751	04/11/00	D'Asaro et al.			
	QP	5,484,664	01/16/96	Kitahara et al.			
	QQ	5,780,311	07/14/98	Beasom et al.			
	QR	6,438,281 B1	08/20/02	Tsukamoto et al.			
	QS	5,399,898	03/21/95	Rostoker			
	QT	6,271,619	08/07/01	Yamada et al.			
	QU	5,334,556	08/02/94	Guldi			
	QV	4,910,164	03/20/90	Shichijo			
	QW	4,952,420	08/28/90	Walters			
	QX	6,121,647	09/19/00	Yano et al.			
	QY	6,306,668 B1	10/23/01	McKee et al.			
	QZ	6,143,366	11/07/00	Lu			
	RA	6,410,941	06/25/02	Taylor et al.			
	RB	5,397,428	03/14/95	Stoner et al.			
	RC	6,432,546 B1	08/13/02	Ramesh et al.			
	RD	6,345,424	02/12/02	Hasegawa et al.			
	RE	6,338,756 B2	01/15/02	Dietze			
	RF	5,516,725	05/14/96	Chang et al.			
	RG	4,667,212	05/19/87	Nakamura			
	RH	5,629,534	05/13/97	Inuzuka et al.			
	RI	3,914,137	10/21/75	Huffman et al.			
	RJ	5,753,928	05/19/98	Krause			
	RK	5,977,567	11/02/99	Verdiell			
	RL	5,130,762	07/14/92	Kulick			
	RM	5,621,227	04/15/97	Joshi			
	RN	6,389,209 B1	05/14/02	Suhir			
	RO	5,163,118	11/10/92	Lorenzo et al.			
	RP	5,926,493	07/20/99	O'Brien et al.			
	RQ	5,323,023	06/21/94	Fork			

Form PTO 1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Robert LEMPKOWSKI, et al.

FILING DATE

August 14, 2001

GROUP

2815

U.S. PATENT DOCUMENTS

INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BWB	SA	6,156,581	12/05/00	Vaudo et al.			
	SB	5,395,663	03/07/95	Tabata et al.			
	SC	4,146,297	03/27/79	Alferness et al.			
	SD	5,452,118	09/19/95	Maruska			
	SE	5,889,296	03/30/99	Imamura et al.			
	SF	6,300,615 B1	10/09/01	Shinohara et al.			
	SG	6,232,910 B1	05/15/01	Bell et al.			
	SH	5,686,741	11/11/97	Ohori et al.			
	SI	4,959,702	09/25/90	Moyer et al			
	SJ	6,100,578	08/08/00	Suzuki			
	SK	6,410,947 B1	06/25/02	Wada			
	SL	6,417,059 B2	07/09/02	Huang			
	SM	6,461,927 B1	10/08/02	Mochizuki et al.			
	SN	6,462,360 B1	10/08/02	Higgins, Jr. et al.			
	SO	5,981,976	11/09/99	Murasato			
	SP	5,981,980	11/09/99	Miyajima et al.			
	SQ	2002/0006245 A1	01/17/02	Kubota et al.			
	SR	2002/0131675 A1	09/19/02	Litvin			
	SS	6,256,426 B1	07/03/01	Duchet			
	ST	6,278,523 B1	08/21/01	Gorecki			
	SU	6,319,730 B1	11/20/01	Ramdani et al.			
	SV	6,404,027	06/11/02	Hong et al.			
	SW	6,312,819 B1	11/06/01	Jia et al.			
	SX	5,119,448	06/02/92	Schaefer et al.			
	SY	4,120,588	10/17/78	Chaum			
	SZ	5,194,917	03/16/93	Regener			
	TA	5,018,816	05/28/91	Murray et al.			
	TB	5,953,468	09/14/99	Finnila et al.			
	TC	5,561,305	10/01/96	Smith			
	TD	5,896,476	04/20/99	Wisseman et al.			
	TE	4,934,777	06/19/90	Jou et al.			
	TF	6,320,238 B1	11/20/01	Kizilyalli et al.			
	TG	6,393,167 B1	05/21/02	Davis et al.			
	TH	5,760,427	06/02/98	Onda			
	TI	6,411,756 B2	06/25/02	Sadot et al.			
	TJ	5,668,048	09/16/97	Kondo et al.			
	TK	5,852,687	12/22/98	Wickham			
	TL	5,122,852	06/16/92	Chan et al.			
	TM	5,173,835	12/22/92	Cornett et al.			
	TN	5,055,835	10/08/91	Sutton			
	TO	6,139,483	10/31/00	Seabaugh et al.			
	TP	5,283,462	02/01/94	Stengel			
	TQ	6,103,403	08/15/00	Grigorian et al.			

Form PTO 442
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

APPLICANT

Robert LEMPKOWSKI, et al.

FILING DATE

August 14, 2001

GROUP

2815

LIST OF REFERENCES CITED BY APPLICANT

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BWB	UA	5,635,433	06/03/97	Sengupta			
	UB	5,427,988	06/27/95	Sengupta et al.			
	UC	6,297,842 B1	10/02/01	Koizumi et al.			
	UD	5,682,046	10/28/97	Takahashi et al.			
	UE	5,181,085	01/19/93	Moon et al.			
	UF	6,051,858	04/18/00	Uchida et al.			
	UG	6,013,553	01/11/00	Wallace et al.			
	UH	4,872,046	10/03/89	Morkoc et al.			
	UI	2002/0047123 A1	04/25/02	Ramdani et al.			
	UJ	5,995,528	11/30/99	Fukunaga et al.			
	UK	5,075,743	12/24/91	Behfar-Rad			
	UL	5,438,584	08/01/95	Paoli et al.			
	UM	4,503,540	03/05/85	Nakashima et al.			
	UN	5,373,166	12/13/94	Buchan et al.			
	UO	6,278,137 B1	08/21/01	Shimoyama et al.			
	UP	5,623,439	04/22/97	Gotoh et al.			
	UQ	4,981,714	01/01/91	Ohno et al.			
	UR	6,194,753 B1	02/27/01	Seon et al.			
	US	6,326,637 B1	12/04/01	Parkin et al.			
	UT						
	UU						
	UV						
	UW						
	UX						
	UY						
	UZ						
	VA						
	VB						
	VC						
	VD						
	VE						
	VF						
	VG						
	VH						
	VI						
	VJ						
	VK						
	VL						
	VM						
	VN						
	VO						
	VP						
	VQ						

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

APPLICANT

Robert LEMPKOWSKI, et al.

FILING DATE

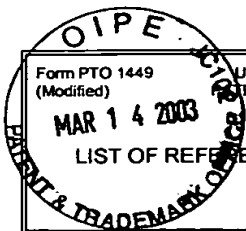
August 14, 2001

GROUP

2815

U.S. PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
DWB	AAA	0 250 171	12/23/87	EP	X	
	AAB	0 342 937	11/23/89	EP	X	
	AAC	0 455 526	06/11/91	EP	X	
	AAD	0 602 568	06/22/94	EP	X	
	AAE	0 607 435	07/27/94	EP	X	
	AAF	1 001 468	05/17/00	EP	X	
	AAG	0 514 018	11/19/92	EP	X	
	AAH	0 999 600	05/10/00	EP	X	
	AAI	1 319 311	06/04/70	Great Britain	X	
	AAJ	5-291299	11/05/93	Japan w/English Abstract	X	
	AAK	11-238683	08/31/99	Japan	X	
	AAL	11-260835	09/24/99	Japan w/English Abstract	X	
	AAM	HEI 2-391	01/05/90	Japan w/English Abstract	X	
	AAN	5-48072	02/26/93	Japan w/English Abstract	X	
	AAO	52-88354	07/23/77	Japan w/English Abstract	X	
	AAP	54-134554	10/19/79	Japan w/English Abstract	X	
	AAQ	55-87424	07/02/80	Japan w/English Abstract	X	
	AAR	61-108187	05/26/86	Japan w/English Abstract	X	
	AAS	6-232126	08/19/94	Japan	X	
	AAT	6-291299	10/18/94	Japan w/English Abstract	X	
	AAU	63-34994	02/15/88	Japan w/English Abstract	X	
	AAV	63-131104	06/03/88	Japan w/English Abstract	X	
	AAW	63-198365	08/17/88	Japan w/English Abstract	X	
	AAX	10-321943	12/04/98	Japan	X	
	AAY	6-334168	12/02/94	Japan	X	
	AAZ	WO 99/63580	12/09/99	WIPO	X	
	ABA	WO 99/14804	03/25/99	WIPO	X	
	ABB	WO 97/45827	12/04/97	WIPO		
	ABC	WO 99/19546	04/22/99	WIPO		
	ABD	WO 00/33363	06/08/00	WIPO		
	ABE	WO 00/48239	08/17/00	WIPO		
	ABF	WO 99/14797	03/25/99	WIPO		
	ABG	GB 2 335 792	09/29/99	Great Britain		
	ABH	1 109 212	06/20/01	Europe		
	ABI	DE 197 12 496	10/30/97	Germany		X
	ABJ	60-212018	10/24/85	Japan w/English Abstract		
	ABK	60-210018	10/22/85	Japan w/English Abstract		
	ABL	WO 92/10875	06/25/92	WIPO		
	ABM	0 682 266	11/15/95	Europe		
	ABN	3-41783	02/91	Japan (English Abstract only)		
	ABO	0 581 239	02/02/94	Europe		
	ABP	0812494	01/16/96	Japan		
	ABQ	2 000 1645	06/16/00	Japan		

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

MAR 14 2003

LIST OF REFERENCES CITED BY APPLICANT

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

APPLICANT

Robert LEMPKOWSKI, et al.

FILING DATE

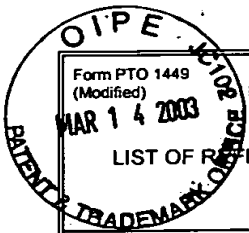
August 14, 2001

GROUP

2815

U.S. PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
BMB	BAA	1 043 426	10/11/00	Europe		
	BAB	2000-068466	03/00	Japan (Abstract)		
	BAC	64-50575	02/27/89	Japan		
	BAD	WO 98/05807	01/12/98	WIPO		
	BAE	WO 94/03908	02/17/94	WIPO		
	BAF	WO 01/33585	05/10/01	WIPO		
	BAG	1-102435	04/20/89	Japan w/English Abstract		
	BAH	52-135684	11/12/77	Japan (English Abstract)		
	BAI	02051220	02/21/90	Japan (English Abstract)		
	BAJ	11135614	05/21/99	Japan (w/English Abstract)		
	BAK	64-52329	02/28/89	Japan (w/English Abstract)		
	BAL	10-256154	09/25/98	Japan (w/English Abstract)		
	BAM	DE 196 07 107	08/28/97	Germany		xx
	BAN	10-303396	11/13/98	Japan (w/English Abstract)		
	BAO	58-213412	12/12/83	Japan w/English Abstract		
	BAP	0 964 259	12/15/99	Europe		
	BAQ	0 875 922	11/04/98	Europe		
	BAR	61-63015	04/01/86	Japan w/English Abstract		
	BAS	11340542	12/10/99	Japan (English Abstract)		
	BAT	WO 01/37330	05/25/01	WIPO		
	BAU	0 331 467	09/06/89	Europe		
	BAV	WO 00/16378	03/23/00	WIPO		
	BAW	0 926 739	06/30/99	Europe		
	BAX	0 964 453	12/15/99	Europe		
	BAY	5-152529	06/18/93	Japan w/English Abstract		
	BAZ	9-67193	03/11/97	Japan w/English Abstract		
	BBA	9-82913	03/28/97	Japan w/English Abstract		
	BBB	0 309 270	03/29/89	Europe		
	BBC	EP 0 957 522	11/17/99	Europe		
	BBD	EP 0 810 666	12/03/97	Europe		
	BBE	1-179411	07/17/89	Japan w/English Abstract		
	BBF	DE 100 17 137	10/26/00	GERMANY		
	BBG	WO 02 01648	01/03/02	WIPO		
	BBH	WO 02/33385 A2	04/25/02	WIPO		
	BBI	WO 01/59814 A2	08/16/01	WIPO		
	BBJ	WO 02/09160 A2	01/31/02	WIPO		
	BBK	WO 00/06812	02/10/00	WIPO		
	BBL	0 483 993	05/06/92	Europe		
	BBM	0 538 611	04/28/93	Europe		
	BBN	WO 01/59820 A1	08/16/01	WIPO		
	BBO	05150143	06/18/93	Japan (English Abstract only)		
	BBP	2 779 843	12/17/99	France		xx
	BBQ	5-086477	04/06/93	Japan (English Abstract only)		

Form PTO 1449
(Modified)

MAR 14 2003

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

LIST OF REFERENCES CITED BY APPLICANT

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

APPLICANT

Robert LEMPKOWSKI, et al.

FILING DATE

August 14, 2001

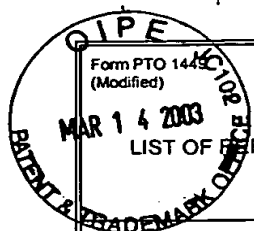
GROUP

2815

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
B2B	CAA	52-89070	07/26/77	Japan	xx	
	CAB	EP 1 069 606	01/17/01	Europe		
	CAC	WO 02/03113	01/10/02	WIPO		
	CAD	WO 02/03467	01/10/02	WIPO		
	CAE	0 630 057	12/21/94	EUROPE		
	CAF	61-36981	02/21/86	Japan w/English Abstract		
	CAG	WO 93/07647	04/15/93	WIPO		
	CAH	2002-9366	01/11/02	Japan w/English Abstract		
	CAI	EP 0 881 669	12/02/98	Europe		
	CAJ	WO 02/03480	01/10/02	WIPO		
	CAK	WO 02/50879	06/27/02	WIPO		
	CAL	EP 0 777 379	06/04/97	Europe		
	CAM	WO 01/04943 A1	01/18/01	WIPO		xx
	CAN	WO 02/47127 A2	06/13/02	WIPO		
	CAO	JP 58-075868	05/07/83	Japan w/English Abstract		
	CAP	EP 0 993 027	04/12/00	Europe		
	CAQ	EP 0 711 853	05/15/96	Europe		
	CAR	WO 98/20606	05/14/98	WIPO		
	CAS	EP 1 043 765	10/11/00	Europe		
	CAT	0 300 499	01/25/89	Europe		
	CAU	EP 1 085 319	03/21/01	Europe		
	CAV	WO 01/16395	03/08/01	WIPO		
	CAW	2000-351692	12/19/00	Japan w/English Abstract		
	CAX	03-188619	08/16/91	Japan (English Abstract only)		
	CAY	63-289812	11/28/88	Japan (English Abstract only)		
	CAZ	EP 0 884 767	12/16/98	Europe		
	CBA	06-069490	03/11/94	Japan (English Abstract only)		
	CBB	WO 01/59821 A1	08/16/01	WIPO		
	CBC					
	CBD					
	CBE					
	CBF					
	CBG					
	CBH					
	CBI					
	CBJ					
	CBK					
	CBL					
	CBM					
	CBN					
	CBO					
	CBP					
	CBQ					

Form PTO 1449 (Modified) MAR 14 2003 LIST OF REFERENCES CITED BY APPLICANT		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 212761US99	SERIAL NO. 09/928,356
APPLICANT Robert LEMPKOWSKI, et al.			FILING DATE August 14, 2001	
GROUP 2815				
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)				
BWB	CCAA	Nakagawara et al., "Effects of Buffer Layers in Epitaxial Growth of SrTiO ₃ Thin Film on Si(100), <i>J. Appl. Phys.</i> , 78 (12), December 15, 1995, pp. 7226-7230.		
	CCAB	Suzuki et al., "A Proposal of Epitaxial Oxide Thin Film Structures For Future Oxide Electronics," <i>Materials Science and Engineering B41</i> , (1996), pp. 166-173.		
	CCAC	W. F. Egelhoff et al., "Optimizing GMR Spin Valves: The Outlook for Improved Properties", <i>1998 Int'l Non Volatile Memory Technology Conference</i> , pp. 34-37.		
	CCAD	Wang et al., "Processing and Performance of Piezoelectric Films", Univ. Of MD, Wilcoxon Research Col, and Motorola Labs, May 11, 2000.		
	CCAE	M. Rotter et al., "Nonlinear Acoustoelectric Interactions in GaAs/LiNbO ₃ Structures", <i>Applied Physics Letters</i> , Vol. 75(7), August 16, 1999, pp. 965-967.		
	CCAF	K. Sreenivas et al., "Surface Acoustic Wave Propagation on Lead Zirconate Titanate Thin Films," <i>Appl. Phys. Lett.</i> 52 (9), Feb. 29, 1998, pp. 709-711.		
	CCAG	M. Rotter et al., "Single Chip Fused Hybrids for Acousto-Electric and Acousto-Optic Applications," <i>1997 Applied Physics Letters</i> , Vol. 70(16), April 21, 1997, pp. 2097-2099.		
	CCAH	A. Mansingh et al., "Surface Acoustic Wave Propagation in PZT/YBCO/SrTiO ₃ and PbTiO ₃ /YBCO/SrTiO ₃ Epitaxial Heterostructures," <i>Ferroelectric</i> , Vol. 224, pages 275-282, 1999.		
	CCAI	S. Mathews et al., "Ferroelectric Field Effect Transistor Based on Epitaxial Perovskite Heterostructures", <i>Science</i> , Vol. 276, April 11, 1997, pp. 238-240.		
	CCAJ	R. Houdre et al., "Properties of GaAs on Si Grown by Molecular Beam Epitaxy," <i>Solid State and Materials Sciences</i> , Vol. 16, Issue 2, 1990, pp. 91-114.		
	CCAK	S. F. Fang et al., "Gallium Arsenide and Other Compound Semiconductors on Silicon," <i>J. Appl. Phys.</i> , 68(7), October 1, 1990, pp. R31-R58.		
	CCAL	Carlin et al., "Impact of GaAs Buffer Thickness on Electronic Quality of GaAs Grown on Graded Ge/GeSi/Si Substrates," <i>Appl. Phys. Letter</i> , Vol. 76, No. 14, April 2000, pp. 1884-1886.		
	CCAM	Ringel et al., "Epitaxial Integration of III-V Materials and Devices with Si Using Graded GeSi Buffers," <i>27th International Symposium on Compound Semiconductors</i> , Oct. 2000.		
	CCAN	Zogg et al., "Progress in Compound-Semiconductor-on-Silicon-Heteroepitaxy with Fluoride Buffer Layers," <i>J. Electrochem Soc.</i> , Vol. 136, No. 3, March 1998, pp. 775-779.		
	CCAO	Xiong et al., "Oxide Defined GaAs Vertical-Cavity Surface-Emitting Lasers on Si Substrates," <i>IEEE Photonics Technology Letters</i> , Vol. 12, No. 2, Feb. 2000, pp. 110-112.		
	CCAP	Clem et al., "Investigation of PZT//LSCO//PV//Aerogel Thin Film Composites for Uncooled Pyroelectric IR Detectors," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 541, pp. 661-666, 1999.		
	CCAQ	Gunapala et al., "Bound-To-Quasi-Bound Quantum-Well Infrared Photodetectors," <i>NASA Tech Brief</i> , Vol. 22, No. 9, September 1998.		
Examiner			Date Considered	
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.				

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

APPLICANT

Robert LEMPKOWSKI, et al.

FILING DATE

August 14, 2001

GROUP

2815

LIST OF REFERENCES CITED BY APPLICANT

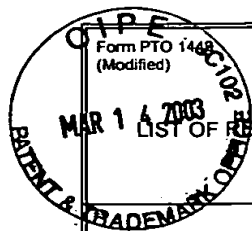
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

BWB	DDAA	Abhay M. Joshi et al., "Monolithic InGaAs-on-silicon Wave Infrared Detector Arrays," <i>Intr. Society for Optical Engineering</i> , Vol. 2999, pp. 211-224.
	DDAB	Bruley et al., "Nanostructure and Chemistry of a (100)MgO/(100) GaAs Interface," <i>Appl. Phys Lett</i> , 65(5), Aug. 1994, pp. 564-566.
	DDAC	Fork et al., "Epitaxial MgO On Si(001) for Y-Ba-Cu-O Thin Film Growth by Pulsed Laser Deposition," <i>Appl. Phys Lett.</i> , 58(20), May 20, 1991, pp. 2294-2296.
	DDAD	Himpsel et al., "Dielectrics on Semiconductors," <i>Materials Science and Engineering</i> , B1(1988), pp. 9-13.
	DDAE	Li et al., "Epitaxial La _{0.87} Sr _{0.33} MnO ₃ Magnetic Tunnel Junctions," <i>J. Appl. Phys.</i> 81(8), Apr. 15, 1997, pp. 5509-5511.
	DDAF	O'Donnell et al., "Colossal Magnetoresistance Magnetic Tunnel Junctions Grown by Molecular-Beam Epitaxy," <i>Appl. Physics Letters</i> , Vol. 76, No. 14, April 3, 2000, pp. 1914-1916.
	DDAG	Mikami et al., "Formation of Si Epi/MgO-Al ₂ O ₃ Epi./SiO ₂ /Si and Its Epitaxial Film Quality," <i>Fundamental Research Laboratories and Microelectronics Laboratories</i> , pp. 31-34, 1983.
	DDAH	T. Asano et al., "An Epitaxial Si/Insulator/Si Structure Prepared by Vacuum Deposition of CaF ₂ and Silicon," <i>Thin Solid Films</i> , Vol. 93 (1982), pp. 143-150.
	DDAI	T. Chikow et al., "Reaction and Regrowth Control of CeO ₂ on Si(111) Surface for the Silicon-On-Insulator Structure," <i>Appl. Phys. Lett.</i> , Vol. 65, No. 8, 22 August 1994, pp. 1030-1032.
	DDAJ	J.F. Kang, et al., "Epitaxial Growth of CeO ₂ (100) Films on Si(100) Substrates by Dual Ion Beams Reactive Sputtering," <i>Solid State Communications</i> , Vol. 108, No. 4, pp. 225-227, 1998.
	DDAK	R.A. Morgan et al., "Vertical-Cavity Surface-Emitting Lasers Come of Age," <i>SPIE</i> , Vol. 2683, pp. 18-29.
	DDAL	"Technical Analysis of Qualcomm QCP-800 Portable Cellular Phone (Transmitter Circuitry)," Talus Corporation, Qualcomm QCP-800 Technical Analysis Report, December 10, 1996, pp. 5-8.
	DDAM	Jo-Ey WONG, et al.; "AN ELECTROSTATICALLY-ACTUATED MEMS SWITCH FOR POWER APPLICATIONS"; IEEE, 2000; pp. 633-638
	DDAN	T. MIZUNO, et al.; "Electron and Hole Mobility Enhancement in Strained-Si MOSFET's on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology"; IEEE ELECTRON DEVICE LETTERS, VOL. 21. NO. 5, MAY 2000; pp. 230-232
	DDAO	F.M. BUFFER, et al.; "Strain-dependence of electron transport in bulk Si and deep-submicron MOSFET's" <i>Computational Electronics</i> , 2000, Book of Abstracts, IWCE Glasgow 2000, 7 th Int'l Workshop on, 2000; pp. 64-65
	DDAP	S.S. LU, et al.; "Piezoelectric field effect transistor (PEFET) using In _{0.2} Ga _{0.8} As/Al _{0.35} Ga _{0.65} As/In _{0.2} Ga _{0.8} As/GaAs Strained layer structure on (111)B GaAs substrate"; <i>ELECTRONICS LETTERS</i> , 12 th Ma 1994, Vol. 30, No. 10; pp. 823-825
	DDAQ	Kihong KIM, et al." On-Chip Wireless Interconnection with Integrated Antennas"; 2000 IEEE; pp. 20.2.1-20.3.4

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

APPLICANT

Robert LEMPKOWSKI, et al.

FILING DATE

August 14, 2001

GROUP

2815

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

BWB	EEAA	G. PASSIOPOULOS, et al.; "V-BAND SINGLE CHIP, DIRECT CARRIER BPSK MODULATION TRANSMITTER WITH INTEGRATED PATCH ANTENNA"; 1998 IEEE MTT-S DIGEST; pp. 305-308
	EEAB	Mau-Chung Frank CHANG, et al.; "RF/Wireless Interconnect for Inter- and Intra-Chip Communications"; Proceedings of the IEEE, Vol. 89, No. 4, April 2001; pp. 456-466
	EEAC	The Electronics Industry Report; Prismark; 2001; pp. 111-120
	EEAD	J.K. ABROKWAH, et al.; "A Manufacturable Complementary GaAs Process"; GaAs IC Symposium, IEEE, 1993; pp. 127-130
	EEAE	H. Nagata, "A Preliminary Consideration of the Growth Behaviour of CeO ₂ , SrTiO ₃ and SrVO ₃ Films on Si Substrate," <i>Thin Solid Films</i> , 224, 1993, pp. 1-3.
	EEAF	Nagata et al., "Heteroepitaxial Growth of CeO ₂ (001) Films on Si(001) Substrates by Pulsed Laser Deposition in Ultrahigh Vacuum," <i>Jpn. Jour. Appl. Phys.</i> , Vol. 30, No. 6B, June 1991, pp. L1136-L1138.
	EEAG	Kado et al., "Heteroepitaxial Growth of SrO Films on Si Substrates," <i>J. Appl. Phys.</i> , 61(6), March 15, 1987, pp. 2398-2400.
	EEAH	H. Ishiwara et al., "Epitaxial Growth of Perovskite Type Oxide Films on Substrates"; <i>Materials Research Symposium Proceedings</i> , Vol. 220, pp. 595-600, April 29 - May 3, 1991.
	EEAI	J.K. Abrokwa, et al.; "A Manufacturable High-Speed Low-Power Complementary GaAs Process"; Extended Abstracts of the 1994 International Conference on Solid State Devices and Materials, Yokohama, 1994, pp.592-594
	EEAJ	C.J. Palmstrom et al.; "Stable and Epitaxial Contacts to III-V Compound Semiconductors"; <i>Contacts to Semiconductors Fundamentals and Technology</i> ; Noyles Publications, 1993; pp.67-150
	EEAK	Jayshri SABARINATHAN, et al.; "Submicron three-dimensional infrared GaAs/Al _x O _y -based photonic crystal using single-step epitaxial growth"; <i>APPLIED PHYSICS LETTERS</i> , VOLUME 78, NUMBER 20, 14 MAY 2001; pp.3024-3026
	EEAL	Philip BALL; "The Next Generation of Optical Fibers"; <i>Technology Review</i> , May 2001; pp.55-61
	EEAM	John D. JOANNOPOULOS, et al.; "Molding the Flow of Light"; <i>Photonic Crystals</i> ; Princeton University Press, 1995
	EEAN	Thomas F. KRAUSS, et al.; "Photonic crystals in the optical regime - past, present and future"; <i>Progress in Quantum Electronics</i> 23 (1999) 51-96
	EEAO	G. H. JIN, et al.; "PLZT Film Waveguide Mach-Zehnder Electrooptic Modulator"; <i>Journal of Lightwave Technology</i> , Vol. 18, No. 6, June 2000; pp.807-812
	EEAP	D.E. ASPNES, et al.; "Steps on (001) silicon surfaces"; <i>J. Vac. Sci. Technol. B</i> , Vol. 5, No. 4, Jul/Aug 1987; pp. 939-944
	EEAQ	D.M. NEWNS, et al.; "Mott transition field effect transistor"; <i>APPLIED PHYSICS LETTERS</i> , VOLUME 73, NUMBER 6, 10 AUGUST 1998; pp.780-782

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

APPLICANT

Robert LEMPKOWSKI, et al.

FILING DATE

August 14, 2001

GROUP

2815

MAR 14 2003

LIST OF REFERENCES CITED BY APPLICANT

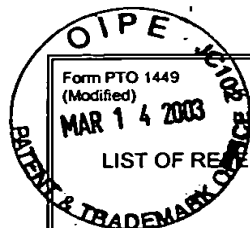
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

BWB	FFAA	Lucent Technologies, Inc. "Arrayed Waveguide Grating Multiplexer/Demultiplexer"; January 2000; 4 pages
1	FFAB	Hisashi SHICHIJO, et al.; "Co-Integration of GaAs MESFET and Si CMOS Circuits"; IEEE ELECTRON DEVICE LETTERS, VOL. 9, NO. 9, SEPTEMBER 1988; pp.444-446
	FFAC	H. SHICHIJO, et al.; "GaAs MESFET and Si CMOS Cointegration and Circuit Techniques"; 1988 IEEE; GaAs IC Symposium - 239-242
	FFAD	H. SHICHIJO, et al.; "Monolithic Process for Co-Integration of GaAs and Silicon Circuits"; 1988 IEEE; pp.778-781
	FFAE	Z.H. ZHU, et al. "Growth of InGaAs multi-quantum wells at 1.3 m wavelength on GaAs compliant substrates"; APPLIED PHYSICS LETTERS, VOLUME 72, NUMBER 20, 18 MAY 1998; pp.2598-2600
	FFAF	Kurt EISENBEISER, et al.; "Metamorphic InAlAs/InGaAs Enhancement Mode HEMT's on GaAs Substrates"; IEEE ELECTRON DEVICE LETTERS, VOL. 20, NO. 10, OCTOBER 1999; pp.507-509
	FFAG	Tomonori NAGASHIMA, et al.; "Three-Terminal Tandem Solar Cells With a Back-Contact Type Bottom Cell" Higashifuji Technical Center, Toyota Motor Corporation; 4 pages
	FFAH	James SCHELLENBERG, et al.; "Low-Loss, Planar Monolithic Baluns for K/Ka-Band Applications"; 1999 IEEE MTT-S Digest; pp.1733-1736
	FFAI	Arnold Leitner et al; "Pulsed Laser Deposition of Superconducting Strontium Titanate Thin-Films"; ; Session K11-Thin Films and Borocarbides; Mixed Session, Wednesday Afternoon; March 19 1997; Room 1202 B, Conv. Center (Abstract)
	FFAJ	R.D. VISPUTE; "High quality optoelectronic grade epitaxial AlN films on -Al ₂ O ₃ , Si and 6H-SiC by pulsed laser deposition"; Thin Solid Films 299 (1997), pp.94-103
	FFAK	T. Warren WEEKS, et al.; "GaN thin films deposited via organometallic vapor phase epitaxy on (6H)-SiC(0001) using high-temperature monocrystalline AlN buffer layers" 320 Applied Physics Letters, Vol. 67, No. 3, 17 July 1995, ppl401-403
	FFAL	Z. YU, et al.; "Epitaxial oxide thin films on Si(001)*"; J. Vac. Sci. Technol. B. Vol. 18, No. 4, Jul/Aug 2000; pp.2139-2145
	FFAM	Gentex Corporate Website; "Photoelectric Smoke Detectors - How They Work; 2001
	FFAN	Jeffrey B. Casady, et al.; "A Hybrid 6H-SiC Temperature Sensor Operational from 25 C to 500 C"; IEEE TRANSACTIONS ON COMPONENTS, PACKAGING, AND MANUFACTURING TECHNOLOGY - PART A, VOL. 19, NO. 3, SEPTEMBER 1996; pp. 416-422
	FFAO	Ronald W. WAYNANT, et al.; "OPTOELECTRONIC INTEGRATED CIRCUITS"; ELECTRO-OPTICS HANDBOOK, McGraw-Hill, Inc., 1994; Chapter Twenty Seven
	FFAP	Antonio MECOZZI, et al.; "The Roles of Semiconductor Optical Amplifiers in Optical Networks"; Optics & Photonics News; March 2001; pp. 37-42
	FFAQ	D.A. FRANCIS, et al.; "A single-chip linear optical amplifier"; OFC, 2001; March 17-22, 2001

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



Form PTO 1449
(Modified)
MAR 14 2003

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

APPLICANT

Robert LEMPKOWSKI, et al.

FILING DATE

August 14, 2001

GROUP

2815

LIST OF REFERENCES CITED BY APPLICANT

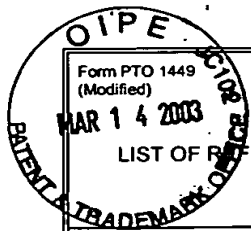
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

bwb	GGAA	G. Vogg et al.; "Epitaxial alloy films of zintl-phase $\text{Ca}(\text{Si}_{1-x}\text{Ge}_x)_2$ "; Journal of Crystal Growth 223 (2001); pp. 573-576
	GGAB	Peter S. GUILFOYLE, et al.; "Optoelectronic Architecture for High-Speed Switching and Processing Applications"; 1998 The Photonics Design and Applications Handbook; pp. H-399-H-406
	GGAC	Gerald B. STRINGFELLOW; "Organometallic Vapor-Phase Epitaxy: Theory and Practice"; Departments of Materials Science and Engineering and Electrical Engineering, University of Utah; Academic Press, 1989
	GGAD	M.A. HERMAN, et al.; "Molecular Beam Epitaxy Fundamentals and Current Status"; Springer-Verlag Berlin Heidelberg, 1989, 1996
	GGAE	"Integration of GaAs on Si Using a Spinel Buffer Layer", IBM Technical Bulletin, Vol. 30, No. 6, Nov. 1987, p. 365.
	GGAF	"GaInAs Superconducting FET", IBM Technical Bulletin, Vol. 36, No. 8, Aug. 1993, p. 655-656.
	GGAG	"Epitaxial 3d Structure Using Mixed Spinel", IBM Technical Bulletin, Vol. 30, No. 3, Aug. 1987, p. 1271.
	GGAH	Moon et al., "Roles of Buffer Layers in Epitaxial Growth of SrTiO_3 Films on Silicon Substrates," <i>Japan J of Appl. Phys.</i> , Vol. 33, March 1994, pp. 1472-1477.
	GGAJ	Yodo et al., GaAs Heteroepitaxial Growth on Si Substrates with Thin Si Interlayers <i>in situ</i> Annealed at High Temperatures," <i>8257b Journal of Vacuum Science & Technology</i> , 1995 May/June, Vol. 13, No. 3, pp. 1000-1005.
	GGAJ	Cuomo et al., "Substrate Effect on the Superconductivity of $\text{YBa}_2\text{Cu}_3\text{O}_7$ Thin Films," AIP Conference 1988, pp. 141-148.
	GGAJ	McKee et al., "Crystalline Oxides on Silicon: The First Five Monolayers," <i>Physical Review Letters</i> , Vol. 81, No. 14, Oct. 1998, pp. 3014-3017.
	GGAL	McKee et al., "Molecular Beam Epitaxy Growth of Epitaxial Barium Silicide, Barium Oxide, and Barium Titanate on Silicon," <i>1991 American Institute of Physics</i> , pp. 782-784, August 13, 1991.
	GGAM	Tambo et al., Molecular Beam Epitaxy Growth of SrTiO_3 Films on $\text{Si}(100)\text{-}2\times 1$ with SrO Buffer Layer," <i>Jpn. J. Appl. Phys.</i> , Vol. 37, 1998, pp. 4454-4459.
	GGAN	McKee et al., "The MBE Growth and Optical Quality of BaTiO_3 and SrTiO_3 Thin Films on MgO ," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 341, April 1994, pp. 309-314.
	GGAO	McKee et al., " BaSi_2 and Thin Film Alkaline Earth Silicides on Silicon," <i>Appl. Phys. Lett.</i> , 63 (20), Nov. 1993, pp. 2818-2820.
	GGAP	McKee et al., "Surface Structures and the Orthorhombic Transformation of Thin Film BaSi_2 on Silicon," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 221, pp. 131-136,
	GGAQ	Brian A. FLOYD, et al.; "The projected Power Consumption of a Wireless Clock Distribution System and Comparison to Conventional Distribution Systems"; IEEE, 1999; pp. IITC99-249-IITC99-250

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

APPLICANT

Robert LEMPKOWSKI, et al.

FILING DATE

August 14, 2001

GROUP

2815

LIST OF REFERENCES CITED BY APPLICANT

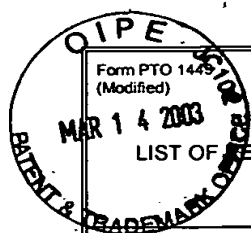
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

BWB	HHAA	Mori et al., "Epitaxial Growth of SrTiO ₃ Films on Si(100) Substrates Using a Focused Electron Beam Evaporation Method," <i>Jpn. J. of Appl. Phys.</i> , Vol. 30, No. 8A, Aug. 1991, pp. L1415-L1417.
	HHAB	Moon et al., "Growth of Crystalline SrTiO ₃ Films on Si Substrates Using Thin Fluoride Buffer Layers and Their Electrical Properties," <i>Jpn. J. of Appl. Phys.</i> , Vol. 33, (1994), pp. 5911-5916.
	HHAC	Farrow et al., "Heteroepitaxy of Dissimilar Materials," <i>Mat. Res. Soc. Symposium Proceedings</i> , Vol. 221, pp. 29-34, April 29 - May 2, 1991.
	HHAD	Ishiwara et al., "Heteroepitaxy on Silicon: Fundamentals, Structure, and Devices," <i>Mat. Res. Soc.</i> , Symposium Proceedings, Vol. 116, pp. 369-374, April 5-8, 1988.
	HHAE	Douglas B. Chrisey, et al; Pulsed Laser Deposition of Thin Films; pp. 273-285
	HHAF	B.A. Block, et al; "Photoluminescence properties of Er ³⁺ -doped BaTiO ₃ thin films"; <i>Appl. Phys. Lett.</i> 65 (1), 4 July 1994, pp. 25-27
	HHAG	Kevin J. Chen et al; "A Novel Ultrafast Functional Device: Resonant Tunneling High Electron Mobility Transistor"; <i>Electron Devices Meeting</i> 1996; IEEE Hong Kong; June 29, 1996; pp. 60-63, XP010210167
	HHAH	Wenhua Zhu et al.; "Molecular Beam Epitaxy of GaAs on Si-on-Insulator"; <i>320 Applied Physics Letters</i> 59(1991) 8 July No. 2; pp. 210-212
	HHAI	Umesh K. Mishra et al; "Oxide Based Compound Semiconductor Electronics"; <i>Electron Devices Meeting</i> ; 1997; Technical Digest, International; Washington, D.C.; 7-10 December 1997; pp. 545-548
	HHAJ	J.M. Daughton et al.; "Applications of Spin Dependent Transport Materials"; <i>J. Phys. D. Appl. Phys.</i> 32(1999) R169-R177
	HHAK	Wei Zhang et al.; "Stress Effect and Enhanced Magnetoresistance in La _{0.67} Ca _{0.33} MnO _{3-δ} Films"; <i>Physical Review, B. Condensed Matter</i> ; American Institute of Physics; Vol. 58, No. 21, Part 1; December 1, 1998; pp. 14143-14146
	HHAL	Q.-Y. Tong et al.; "IOS-a new type of materials combination for system-on-a chip preparation"; <i>1999 IEEE International SOI Conference</i> , Oct. 1999; pp.104-105
	HHAM	T. Kanninen et al.; "Growth of Dielectric 1hfo2/Ta2O5 Thin Film Nanolaminate Capacitors By Atomic Layer Epitaxy"; <i>Electrochemical Society Proceedings</i> , U.S. Electrochemical Society; Pennington, N.J.; August 31, 1997; pp. 36-46
	HHAN	Myung Bok Lee; "Heteroepitaxial Growth of BaTiO ₃ Films on Si by Pulsed Laser Deposition"; <i>Applied Physics Letters</i> ; March 13, 1995; pp. 1331-1333
	HHAO	Myung Bok Lee; "Formation and Characterization of Eptiaxial TiO ₂ and BaTiO ₃ /TiO ₂ Films on Si Substrate"; <i>Japan Journal Applied Physics Letters</i> ; Vol. 34; 1995; pp. 808-811
	HHAP	Gilbert Lecarpentier et al.; "High Accuracy Machine Automated Assembly for Opto Electronics"; <i>2000 Electronic Components and Technology Conference</i> ; pp. 1-4
	HHAQ	R. Ramesh; "Ferroelectric La-Sr-Co-O/Pb-Zr-Ti-O/La-Sr-Co-O Heterostructures on Silicon via Template Growth"; <i>320 Applied Physics Letters</i> ; 63(1993); 27 December; No. 26; pp. 3592-3594

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

APPLICANT

Robert LEMPKOWSKI, et al.

FILING DATE

August 14, 2001

GROUP

2815

LIST OF REFERENCES CITED BY APPLICANT

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

blwb	IIAA	K. Eisenbeiser; "Field Effect Transistors with SrTiO ₃ Gate Dielectric on Si"; Applied Physics Letters; Vol. 76, No. 10; March 6, 2000; pp. 1324-1326
	IIAB	Stephen A. Mass; "Microwave Mixers"; Second Edition; 2pp.
	IIAC	Douglas J. Hamilton et al.; "Basic Integrated Circuit Engineering"; pp.2; 1975
	IIAD	Takeshi Obata; "Tunneling Magnetoresistance at Up to 270 K in La _{0.8} Sr _{0.2} MnO ₃ /SrTiO ₃ /La _{0.8} Sr _{0.2} MnO ₃ Junctions with 1.6-nm-Thick Barriers"; Applied Physics Letters; Vol. 74, No. 2; 11 January 1999; pp. 290-292
	IIAE	Wei Zhang et al.; "Enhanced Magnetoresistance in La-Ca-Mn-O Films on Si Substrates Using YbaCuO/CeO ₂ Heterostructures"; Physica C; Vol. 282-287, No. 2003; 1 August 1997; pp. 1231-1232
	IIAF	Shogo Imada et al; "Epitaxial Growth of Ferroelectric YmnO ₃ Thin Films on Si (111) Substrates by Molecular Beam Epitaxy"; Jpn. J. Appl. Phys. Vol. 37 (1998); pp. 6497-6501; Part 1, No. 12A, December 1998
	IIAG	Ladislav Pust et al.; "Temperature Dependence of the Magnetization Reversal in Co(fcc)-BN-Co(poly hcp) Structures"; Journal of Applied Physics; Vol. 85, No. 8; 15 April 1999; pp. 5765-5767
	IIAH	C. Martinez; "Epitaxial Metallic Nanostructures on GaAs"; Surface Science; Vol. 482-485; pp. 910-915; 2001
	IIAI	Wen-Ching Shih et al.; "Theoretical Investigation of the SAW Properties of Ferroelectric Film Composite Structures"; IEEE Transactions of Ultrasonics, Ferroelectrics, and Frequency Control; Vol. 45, No. 2; March 1998; pp. 305-316
	IIAJ	Zhu Dazhong et al.; "Design of ZnO/SiO ₂ /Si Monolithic Integrated Programmable SAW Filter"; Proceedings of Fifth International Conference on Solid-State and Integrated Circuit Technology; 21-23; October 1998; pp. 826-829
	IIAK	Kirk-Othmer Encyclopedia of Chemical Technology; Fourth Edition, Vol. 12; Fuel Resources to Heat Stabilizers; A Wiley-Interscience Publication; John Wiley & Sons
	IIAL	Joseph W. Goodman et al; "Optical Interconnections For VLSI Systems"; Proceedings of the IEEE, Vol. 72, No. 7 July 1984
	IIAM	Fathimulla et al.; "MONOLITHIC INTEGRATION OF InGaAs/InAlAs MODFETs and RTDs on InP-bonded-to Si SUBSTRATE"; Fourth International Conference on Indium Phosphide and Related Materials, Newport, RI, USA; April 21-24, 1992 ; pp. 167-170; XP000341253; IEEE, New York, NY, USA; ISBN: 0-7803-0522-1
	IIAN	H. Takahashi et al.; "Arrayed-Waveguide Grating For Wavelength Division Multi/Demultiplexer With Nanometre Resolution"; Electronics Letters; Vol. 26., No. 2, 18th January 1990
	IIAO	Pierret, R.F.; "1/J-FET and MESFET"; Field Effect Devices; MA, Addison-Wesley; 1990; pp. 9-22
	IIAP	M. Schreiter, et al.; "Sputtering of Self-Polarized PZT Films for IR-Detector Arrays"; 1998 IEEE; pp. 181-185
	IIAQ	Hideaki Adachi et al.; "Sputtering Preparation of Ferroelectric PLZT Thin Films and Their Optical Applications"; IEEE Transactions of Ultrasonics, Ferroelectrics and Frequency Control, Vol. 38, No. 6, November 1991

Examiner

Date Considered

*Examiner: initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO 1449 (Modified) MAR 14 2003 LIST OF REFERENCES CITED BY APPLICANT	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 212761US99 APPLICANT Robert LEMPKOWSKI, et al. FILING DATE August 14, 2001	SERIAL NO. 09/928,356 GROUP 2815
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)			
BNB	JJAA JJAB JJAC JJAD JJAE JJAF JJAG JJAH JJAI JJAJ JJAK JJAL JJAM JJAN JJAO JJAP JJAQ	A.J. Moulson et al.; "Electroceramics Materials Properties Applications"; Chapman & Hall; pp. 366-369 P.A. Langjahr et al.; "Epitaxial Growth and Structure of Cubic and Pseudocubic Perovskite Films on Perovskite Substrates"; Mat. Res. Soc. Symp. Proc., Vol. 401; 1995 Materials Research Society; pp. 109-114 Wang et al.; "Depletion-Mode GaAs MOSFETs with Negligible Drain Current Drift and Hysteresis"; Electron Devices Meeting, 1998, IEDM '98 Technical Digest; pp. 67-70 Ben G. Streetman; "Solid State Electronic Devices"; 1990, Prentice Hall; Third Edition; pp. 320-322 A.Y Wu et al.; "Highly Oriented (Pb,La)(Zr,Ti)O ₃ Thin Films on Amorphous Substrates"; IEEE, 1992; pp. 301-304 Timothy E. Glassman et al.; "Evidence for Cooperative Oxidation of MoCVD Precursors Used in Ba _x Sr _{1-x} TiO ₃ Film Growth"; Mat. Res. Soc. Symp. Proc. Vol. 446, 1997 Materials Research Society; pp. 321-326 S.N. Subbarao et al.; "Monolithic PIN Photodetector and FET Amplifier on GaAs-os-Si"; IEEE; GaAs IC Symposium-163-166; 1989 T.A. Langdo et al.; "High Quality Ge on Si by Epitaxial Necking"; Applied Physics Letters; Vol. 76, No. 25; pp. 3700-3702; June 19, 2000 Chenning Hu et al.; Solar Cells From Basics to Advanced Systems; McGraw-Hill Book Company; 1983 O.J. Painter et al; "Room Temperature Photonic Crystal Defect Lasers at Near-Infrared Wavelengths in InGaAsP"; Journal of Lightwave Technology, Vol. 17, No. 11; November 1999 C. Donn et al.; "A 16-Element, K-Band Monolithic Active Receive Phased Array Antenna"; Antennas and Propagation Society International Symposium, 1988; pp.188-191, Vol. 1; 6-10 June 1988 Don W. Shaw; "Epitaxial GaAs on Si: Progress and Potential Applications"; Mat. Res. Soc. Symp. Proc.; pp.15-30; 1987 G.J.M. Dormans, et al.; "PbTiO ₃ /Thin Films Grown by Organometallic Chemical Vapour Deposition"; Third International Symposium on Integrated Ferroelectrics; April 3-5, 1991 (Abstract) P.J. Borrelli et al.; "Compositional and Structural Properties of Sputtered PLZT Thin Films"; Ferroelectric Thin Films II Symposium; Dec. 2-4, 1991 (Abstract) Ranu Nayak et al; "Enhanced acousto-optic diffraction efficiency in a symmetric SrTiO ₃ /BaTiO ₃ /SrTiO ₃ thin-film heterostructure"; 1 November 2000; Vol. 39, No. 31; Applied Optics; pp. 5847-5853 Ranu Nayak et al; "Studies on acousto-optical interaction in SrTiO ₃ /BaTiO ₃ /SrTiO ₃ epitaxial thin film heterostructures"; J. Phys. D: Appl. Phys. 32 (1999) 380-387 S.K. Tewksbury et al.; "Cointegration of Optoelectronics and Submicron CMOS"; Wafer Scale Integration; 1993; Proceedings, Fifth Annual IEEE; 20 January 1993; pp. 358-367	
Examiner	Date Considered		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

212761US99

SERIAL NO.

09/928,356

MAR 14 2003

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Robert LEMPKOWSKI, et al.

FILING DATE

August 14, 2001

GROUP

2815

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

KKAA	V. Kaushik et al.; "Device Characteristics of Crystalline Epitaxial Oxides on Silicon"; Device Research Conference, 2000; Conference Digest 58th DRC; pp. 17-20; June 19-21, 2000
KKAB	Katherine Derbyshire; "Prospects Bright for Optoelectronics Volume, Cost Drive Manufacturing for Optical Applications"; Semiconductor Magazine; Vol. 3, No. 3; March 2002
KKAC	Alex Chediak et al; "Integration of GaAs/Si with Buffer Layers and Its Impact on Device Integration"; TICS 4, Prof. Sands. MSE 225, April 12, 2002; pp. 1-5
KKAD	S.A. Chambers et al; "Band Discontinuities at Epitaxial SrTiO ₃ /Si(001) Heterojunctions"; Applied Physics Letters; Vol. 77, No. 11; September 11, 2000; pp. 1662-1664
KKAE	H. Wang et al.; "GaAs/GaAlAs Power HBTs for Mobile Communications"; Microwave Symposium Digest; 1993 IEEE; Vol. 2.; pp. 549-552
KKAF	Y. Ota et al.; "Application of Heterojunction FET to Power Amplifier for Cellular Telephone"; Electronics Letters; 26th May 1994; Vol. 30, No. 11; pp. 906-907
KKAG	Keiichi Sakuno et al; "A 3.5W HBT MMIC Power Amplifier Module for Mobile Communications"; IEEE 1994; Microwave and Millimeter-Wave Monolithic Circuits Symposium; pp. 63-66
KKAH	Mitsubishi Semiconductors Press Release (GaAs FET's) November 8, 1999 pp.1-2
KKAI	R.J. Matyi et al; "Selected Area Heteroepitaxial Growth of GaAs on Silicon for Advanced Device Structures"; 2194 Thin Solid Films; 181 (1989) December 10; No. 1; pp. 213-225
KKAJ	K. Nashimoto et al; "Patterning of Nb, LaOnZr, TiO ₃ Waveguides for Fabricating Micro-Optics Using Wet Etching and Solid-Phase Epitaxy"; Applied Physics Letters; Vol. 75, No. 8; 23 August 1999; pp. 1054-1056
KKAK	Bang-Hung Tsao et al; "Sputtered Barium Titanate and Barium Strontium Titanate Films for Capacitor Applications"; Applications of Ferroelectrics, 2000; Proceedings of the 2000 12th International Symposium on Vol. 2; pp. 837-840
KKAL	Man Fai Ng et al; "Heteroepitaxial growth of lanthanum aluminate films derived from mixed metal nitrates"; Journal of Materials Research; Vol. 12, No. 5; pp. 1306
KKAM	Yuji Matsumoto et al.; "Room-Temperature Ferromagnetism in Transparent Transition Metal-Doped Titanium Dioxide"; Science; 2 February 2001; Vol. 291; pp. 854-856
KKAN	S.A. Chambers et al.; "Epitaxial Growth and Properties of Ferromagnetic Co-Doped TiO ₂ Anatase"; Applied Physics Letters; Vol. 79, No. 21; November 19, 2001; pp. 3467-3469
KKAO	
KKAP	
KKAQ	

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.